

# 采用双随机展频技术的 LM5156x 2.2MHz 宽输入电压 65V 非同步升压/SEPIC/反激式控制器

## 1 特性

- 提供功能安全
  - 可帮助进行功能安全系统设计的文档
- 适用于具有宽输入工作电压范围的电池应用
  - 3.5V 至 60V 工作电压范围 (绝对最大值 65V)
  - 当 BIAS = VCC 时, 为 2.97V 至 16V
  - BIAS 电压大于等于 3.5V 时最小升压电源电压为 1.5V
  - 高达 65V 的输入瞬态保护
  - 最小电池消耗
    - 低关断电流 ( $I_Q \leq 2.6\mu A$ )
    - 低工作电流 ( $I_Q \leq 490\mu A$ )
- 解决方案尺寸小、成本低
  - 最大开关频率为 2.2MHz
  - 12 引脚 WSON 封装 (3mm × 2mm)
  - 集成的误差放大器支持在没有光耦合器的情况下进行初级侧稳压 (反激)
- 减缓 EMI
  - 可选双随机展频
  - 无引线封装
- 低功耗、高效率
  - 100mV ±7% 精确限流阈值
  - 强大的 1.5A 峰值标准 MOSFET 驱动器
  - 支持外部 VCC 电源
- 避免 AM 频带干扰和串扰
  - 可选的时钟同步
  - 100kHz 至 2.2MHz 的动态可编程开关频率
- 集成型保护特性
  - 在输入电压范围内具有恒定峰值电流限制
  - 可选断续模式过载保护 (参阅 [器件比较表](#))
  - 可编程线路 UVLO
  - OVP 保护
  - 热关断保护
- ±1% 精度反馈基准
- 支持附加斜坡补偿
- 可编程软启动
- PGOOD 指示器
- 使用 LM5156x 并借助 [WEBENCH® Power Designer](#) 创建定制设计方案

## 2 应用

- 无光耦合器的多输出反激式应用
- LED 偏置电源
- 宽输入升压、SEPIC 和反激式电源模块
- 便携式扬声器应用
- 反激式 POE 电源应用
- 电池供电的升压、SEPIC 和反激式应用

## 3 说明

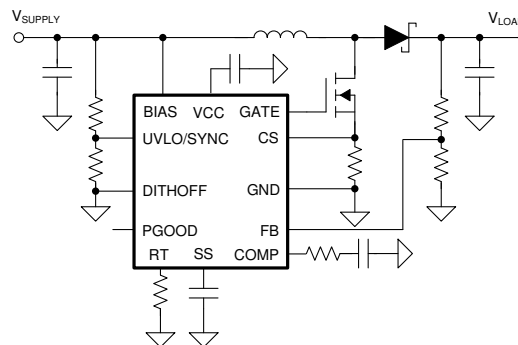
LM5156x (LM5156 和 LM51561) 器件是一款采用峰值电流模式控制、具有宽输入范围的非同步升压控制器。该器件可用于升压、SEPIC 和反激式拓扑。

如果 BIAS 引脚连接到 VCC 引脚, 则 LM5156x 器件可由单节电池 (最低电压 2.97V) 供电。如果 BIAS 引脚电压高于 3.5V, 则该器件可使用低至 1.5V 的输入电源电压。

### 器件信息

器件型号	封装 <sup>(1)</sup>	封装尺寸 (标称值)
LM5156	WSON (12)	3.00mm × 2.00mm
LM51561		

- (1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。



典型升压应用



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## 4 Revision History

DATE	REVISION	NOTES
January 2021	*	Initial release.

## 5 Description (continued)

The internal VCC regulator also supports BIAS pin operation up to 60 V (65-V absolute maximum) . The switching frequency is dynamically programmable with an external resistor from 100 kHz to 2.2 MHz. Switching at 2.2 MHz minimizes AM band interference and allows for a small solution size and fast transient response. To reduce the EMI of the power supply, the device provides a selectable dual random spread spectrum which reduces the EMI over the wide frequency range.

The device features a 1.5-A standard MOSFET driver and a low 100-mV current limit threshold. The device also supports the use of an external VCC supply to improve efficiency. Low operating current and pulse-skipping operation improve efficiency at light loads.

The device has built-in protection features such as cycle-by-cycle current limit, overvoltage protection, line UVLO, and thermal shutdown. Hiccup mode overload protection is available in the LM51561 device option. Additional features include low shutdown  $I_Q$ , programmable soft start, programmable slope compensation, precision reference, power-good indicator, and external clock synchronization.

## 6 Device Comparison Table

DEVICE OPTION	HICCUP MODE PROTECTION	INTERNAL REFERENCE
LM5156	Disabled	1 V
LM51561	Enabled	1 V

## 7 Pin Configuration and Functions

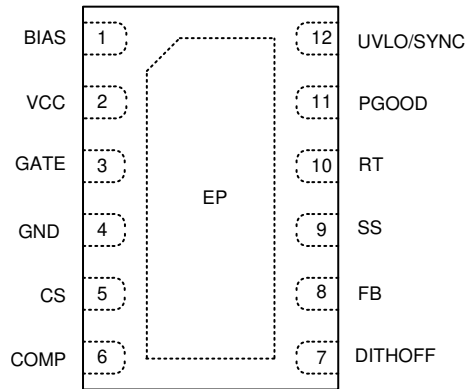


图 7-1. 12-Pin WSON DSS Package (Transparent Top View)

表 7-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NO.	NAME		
1	BIAS	P	Supply voltage input to the VCC regulator. Connect a bypass capacitor from this pin to GND.
2	VCC	P	Output of the internal VCC regulator and supply voltage input of the MOSFET driver. Connect a ceramic bypass capacitor from this pin to GND.
3	GATE	O	N-channel MOSFET gate drive output. Connect directly to the gate of the N-channel MOSFET through a short, low inductance path.
4	GND	G	Ground pin. Connect directly to the ground connection of the sense resistor through a low inductance wide and short path.
5	CS	I	Current sense input pin. Connect to the positive side of the current sense resistor through a short path.
6	COMP	O	Output of the internal transconductance error amplifier. Connect the loop compensation components between this pin and GND.
7	DITHOFF	I	Spread spectrum selection pin. Internal spread spectrum (Clock dithering) is disabled when the pin is connected to the VCC pin. Connecting the pin to GND enables the internal spread spectrum.
8	FB	I	Inverting input of the error amplifier. Connect a voltage divider from the output to this pin to set output voltage in boost/SEPIC topologies. Connect the low-side feedback resistor to GND.
9	SS	I	Soft-start time programming pin. An external capacitor and an internal current source set the ramp rate of the internal error amplifier reference during soft start. Connect the ground connection of the capacitor to GND.
10	RT	I	Switching frequency setting pin. The switching frequency is programmed by a single resistor between RT and GND.
11	PGOOD	O	Power-good indicator. An open-drain output which goes low if FB is below the under voltage threshold. Connect a pullup resistor to the system voltage rail.
12	UVLO/ SYNC/EN	I	Undervoltage lockout programming pin. The converter start-up and shutdown levels can be programmed by connecting this pin to the supply voltage through a resistor divider. The internal clock can be synchronized to an external clock by applying a negative pulse signal into the UVLO/ SYNC/EN pin. This pin must not be left floating. Connect to BIAS pin if not used. Connect the low-side UVLO resistor to GND.
—	EP	—	Exposed pad of the package. The exposed pad must be connected to GND and the large ground copper plane to decrease thermal resistance.

(1) G = Ground, I = Input, O = Output, P = Power

## 8 Specifications

### 8.1 Absolute Maximum Ratings

Over the recommended operating junction temperature range<sup>(1)</sup>

		MIN	MAX	UNIT
Input	BIAS to GND	- 0.3	65	V
	UVLO to GND	- 0.3	$V_{BIAS}+0.3$	
	SS to GND <sup>(2)</sup>	- 0.3	3.8	
	RT to GND <sup>(2)</sup>	- 0.3	3.8	
	FB to GND	- 0.3	4.0	
	CS to GND(DC)	- 0.3	0.3	
	CS to GND(50ns transient)	- 1		
	DITHOFF to GND	-0.3	18	
Output	VCC to GND	- 0.3	18 <sup>(3)</sup>	V
	GATE to GND (50ns transient)	- 1		
	PGOOD to GND <sup>(4)</sup>	- 0.3	18	
	COMP to GND <sup>(5)</sup>	- 0.3		
Junction temperature, $T_J$ <sup>(6)</sup>		- 40	150	°C
Storage temperature, $T_{stg}$		- 55	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) This pin is not specified to have an external voltage applied.
- (3) 18 V or  $V_{BIAS} + 0.3$  V whichever is lower
- (4) The maximum current sink is limited to 1 mA when  $V_{PGOOD} > V_{BIAS}$ .
- (5) This pin has an internal max voltage clamp which can handle up to 1.6 mA.
- (6) High junction temperatures degrade operating lifetimes. Operating lifetime is de-rated for junction temperatures greater than 125°C.

### 8.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 8.3 Recommended Operating Conditions

Over the recommended operating junction temperature range<sup>(1)</sup>

		MIN	NOM	MAX	UNIT
V <sub>BIAS</sub>	Bias input <sup>(2)</sup>	2.97		60	V
V <sub>VCC</sub>	VCC voltage <sup>(3)</sup>	2.97		16	V
V <sub>DITHOFF</sub>	DITHOFF input	0		16	V
V <sub>UVLO</sub>	UVLO input	0		60	V
V <sub>FB</sub>	FB input	0		4.0	V
f <sub>SW</sub>	Typical switching frequency	100		2200	kHz
f <sub>SYNC</sub>	Synchronization pulse frequency	100		2200	kHz
T <sub>J</sub>	Operating junction temperature	- 40		125	°C

- (1) [Operating Ratings](#) are conditions under the device is intended to be functional. For specifications and test conditions, see [Electrical Characteristics](#).
- (2) BIAS pin operating range is from 2.97 V to 16 V when VCC is directly connected to BIAS. BIAS pin operating range is from 3.5 V to 60 V when VCC is supplied from the internal VCC regulator.
- (3) This pin voltage should be less than V<sub>BIAS</sub> + 0.3 V.

### 8.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		LM5156x	UNIT
		DSS(WSON)	
		12 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance (LM5156EVM-BST)	41.5	°C/W
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	63.1	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	62.4	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	31.6	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter (LM5156EVM-BST)	1.5	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	2.2	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter (LM5156EVM-BST)	21.8	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	31.5	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	10.7	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

### 8.5 Electrical Characteristics

Typical values correspond to T<sub>J</sub> = 25°C. Minimum and maximum limits apply over T<sub>J</sub> = -40°C to 125°C. Unless otherwise stated, V<sub>BIAS</sub> = 12 V, R<sub>T</sub> = 9.09 kΩ

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENT</b>					
I <sub>SHUTDOWN(BIAS)</sub>	BIAS shutdown current V <sub>BIAS</sub> = 12 V, V <sub>UVLO</sub> = 0 V		2.6	5	uA
I <sub>OPERATING(BIAS)</sub>	BIAS operating current V <sub>BIAS</sub> = 12 V, V <sub>UVLO</sub> = 2.0 V, V <sub>FB</sub> = V <sub>REF</sub> , R <sub>T</sub> = 220 kΩ		490	550	uA
<b>VCC REGULATOR</b>					
V <sub>VCC-REG</sub>	VCC regulation V <sub>BIAS</sub> = 8 V, No load	6.5	6.85	7	V
	VCC regulation V <sub>BIAS</sub> = 8 V, I <sub>VCC</sub> = 35 mA	6.5			V
V <sub>VCC-UVLO(RISING)</sub>	VCC UVLO threshold VCC rising	2.75	2.85	2.95	V
	VCC UVLO hysteresis VCC falling		0.063		V
I <sub>VCC-CL</sub>	VCC sourcing current limit V <sub>BIAS</sub> = 10 V, V <sub>VCC</sub> = 0 V	35	110		mA
<b>ENABLE</b>					

Typical values correspond to  $T_J = 25^\circ\text{C}$ . Minimum and maximum limits apply over  $T_J = -40^\circ\text{C}$  to  $125^\circ\text{C}$ . Unless otherwise stated,  $V_{\text{BIAS}} = 12\text{ V}$ ,  $R_T = 9.09\text{ k}\Omega$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{\text{EN(RISING)}}$	Enable threshold	EN rising	0.4	0.52	0.7	V
$V_{\text{EN(FALLING)}}$	Enable threshold	EN falling	0.33	0.49	0.63	V
$V_{\text{EN(HYS)}}$	Enable hysteresis	EN falling		0.03		V
<b>UVLO/SYNC</b>						
$V_{\text{UVLO(RISING)}}$	UVLO / SYNC threshold	UVLO rising	1.425	1.5	1.575	V
$V_{\text{UVLO(FALLING)}}$	UVLO / SYNC threshold	UVLO falling	1.370	1.45	1.520	V
$V_{\text{UVLO(HYS)}}$	UVLO / SYNC threshold hysteresis	UVLO falling		0.05		V
$I_{\text{UVLO}}$	UVLO hysteresis current	$V_{\text{UVLO}} = 1.6\text{ V}$	4	5	6	$\mu\text{A}$
<b>SPREAD SPECTRUM</b>						
$V_{\text{DITHOFF(RISING)}}$	Clock dithering threshold	DITHOFF rising, $V_{\text{BIAS}} = 4\text{ V}$	1.1	1.7	2.1	V
$V_{\text{DITHOFF(FALLING)}}$	Clock dithering threshold	DITHOFF falling, $V_{\text{BIAS}} = 4\text{ V}$	0.6	1.2	1.8	V
$V_{\text{DITHOFF(HYS)}}$	Clock dithering threshold hysteresis	DITHOFF falling, $V_{\text{BIAS}} = 4\text{ V}$		0.5		V
<b>SS</b>						
$I_{\text{SS}}$	Soft-start current		9	10	11	$\mu\text{A}$
	SS pull-down switch $R_{\text{DS(on)}}$			55		$\Omega$
<b>PULSE WIDTH MODULATION</b>						
fsw1	Switching frequency	$R_T = 220\text{ k}\Omega$ , $V_{\text{BIAS}} = 4\text{ V}$	85	100	115	kHz
fsw2	Switching frequency	$R_T = 9.09\text{ k}\Omega$ , $V_{\text{BIAS}} = 4\text{ V}$	1980	2200	2420	kHz
$t_{\text{ON(MIN)}}$	Minimum on-time	$R_T = 9.09\text{ k}\Omega$		50		ns
$D_{\text{MAX1}}$	Maximum duty cycle limit	$R_T = 9.09\text{ k}\Omega$ , $V_{\text{BIAS}} = 4\text{ V}$	80	85	90	%
$D_{\text{MAX2}}$	Maximum duty cycle limit	$R_T = 220\text{ k}\Omega$ , $V_{\text{BIAS}} = 4\text{ V}$	90	93	96	%
<b>CURRENT SENSE</b>						
$I_{\text{SLOPE}}$	Peak slope compensation current	$R_T = 220\text{ k}\Omega$	22.5	30	37.5	$\mu\text{A}$
$V_{\text{CLTH}}$	Current Limit threshold (CS-GND)		93	100	107	mV
<b>HICCUP MODE PROTECTION (LM51561)</b>						
	Hiccup enable cycles			64		Cycles
	Hiccup timer reset cycles			8		Cycles
<b>ERROR AMPLIFIER</b>						
$V_{\text{REF}}$	FB reference	LM5156, LM51561	0.99	1	1.01	V
$G_m$	Transconductance			2		$\text{mA/V}$
	COMP sourcing current	$V_{\text{COMP}} = 1.2\text{ V}$	180			$\mu\text{A}$
	COMP clamp voltage	COMP rising ( $V_{\text{UVLO}} = 2.0\text{ V}$ )	2.5	2.8		V
	COMP clamp voltage	COMP falling		1	1.1	V
<b>OVP</b>						
$V_{\text{OVTH}}$	Over-voltage threshold	FB rising (referece to $V_{\text{REF}}$ )	107	110	113	%
	Over-voltage threshold	FB falling (referece to $V_{\text{REF}}$ )		105		%
<b>PGOOD</b>						
	PGOOD pulldown switch $R_{\text{DS(on)}}$	1 mA sinking		90		$\Omega$
$V_{\text{UVTH}}$	Under-voltage threshold	FB falling (referece to $V_{\text{REF}}$ )	87	90	93	%
	Under-voltage threshold	FB rising (referece to $V_{\text{REF}}$ )		95		%
<b>MOSFET DRIVER</b>						
	High-state voltage drop	100 mA sinking		0.25		V
	Low-state voltage drop	100 mA sourcing		0.15		V

Typical values correspond to  $T_J = 25^{\circ}\text{C}$ . Minimum and maximum limits apply over  $T_J = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ . Unless otherwise stated,  $V_{\text{BIAS}} = 12\text{ V}$ ,  $R_T = 9.09\text{ k}\Omega$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>THERMAL SHUTDOWN</b>						
$T_{\text{TSD}}$	Thermal shutdown threshold	Temperature rising		175		$^{\circ}\text{C}$
	Thermal shutdown hysteresis			15		$^{\circ}\text{C}$



## 8.6 Typical Characteristics

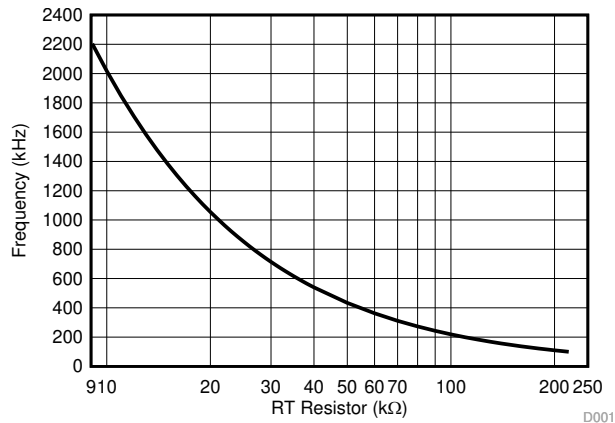


图 8-1. Frequency vs RT Resistance

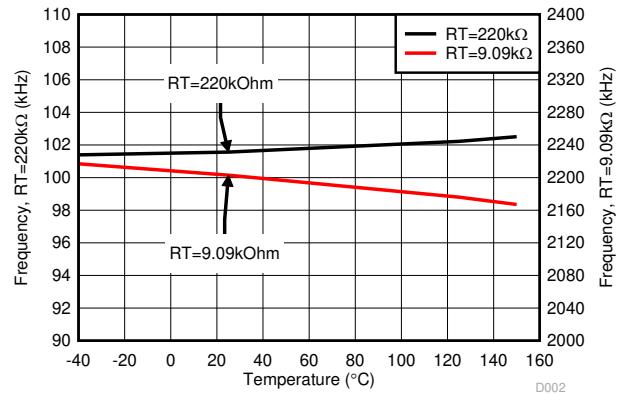


图 8-2. Frequency vs Temperature

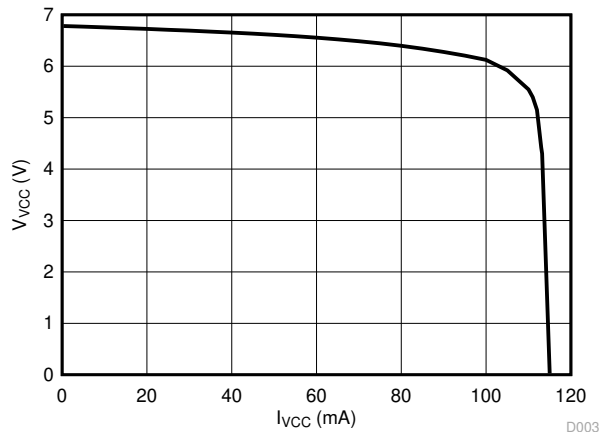


图 8-3.  $V_{VCC}$  vs  $I_{VCC}$

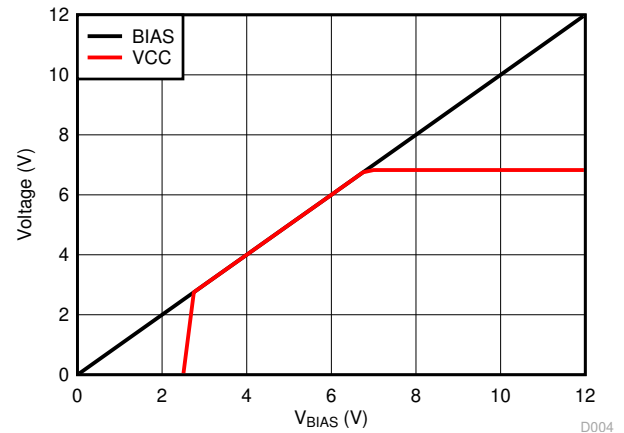


图 8-4.  $V_{VCC}$  vs  $V_{BIAS}$  (No Load)

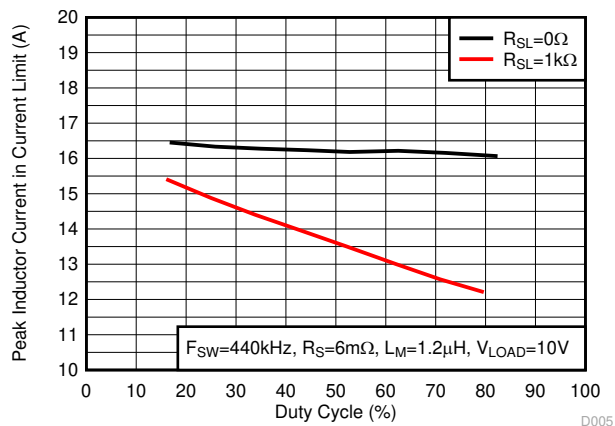


图 8-5. Peak Current Limit vs Duty Cycle

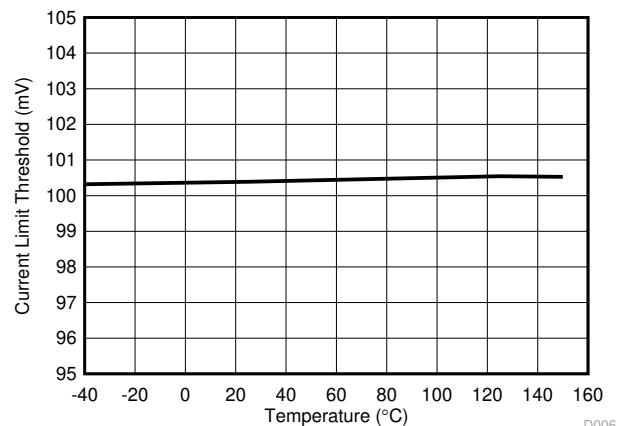


图 8-6. Current Limit Threshold vs Temperature

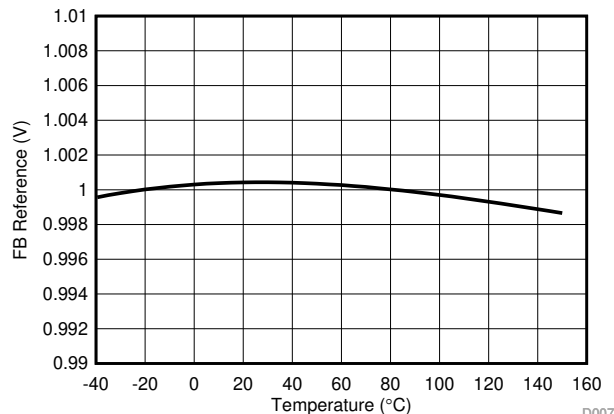


图 8-7. FB Reference vs Temperature

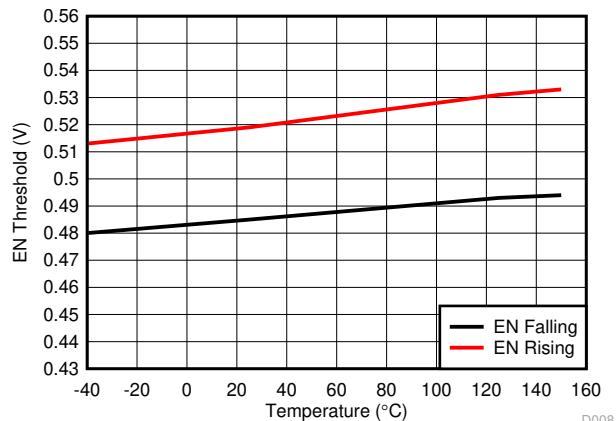


图 8-8. EN Threshold vs Temperature

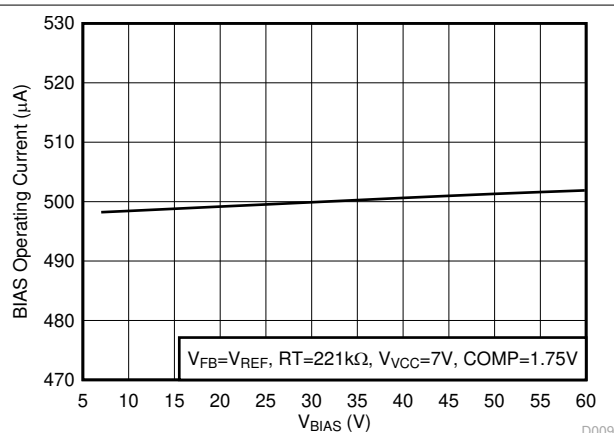


图 8-9.  $I_{\text{OPERATING(BIAS)}}$  Including RT Current vs  $V_{\text{BIAS}}$

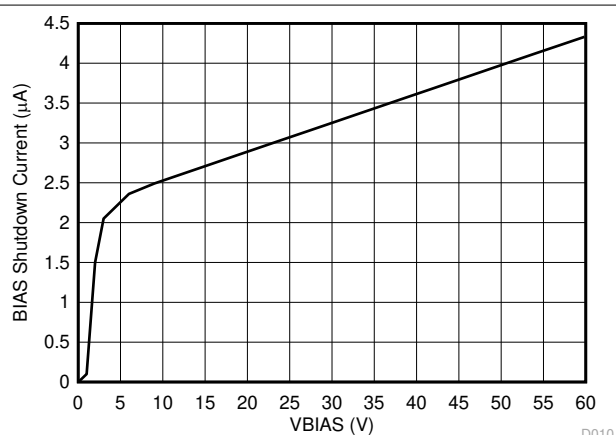


图 8-10.  $I_{\text{SHUTDOWN(BIAS)}}$  vs  $V_{\text{BIAS}}$

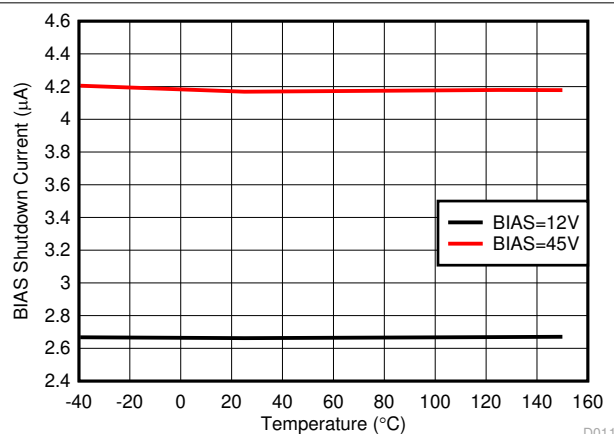


图 8-11.  $I_{\text{SHUTDOWN}}$  vs Temperature

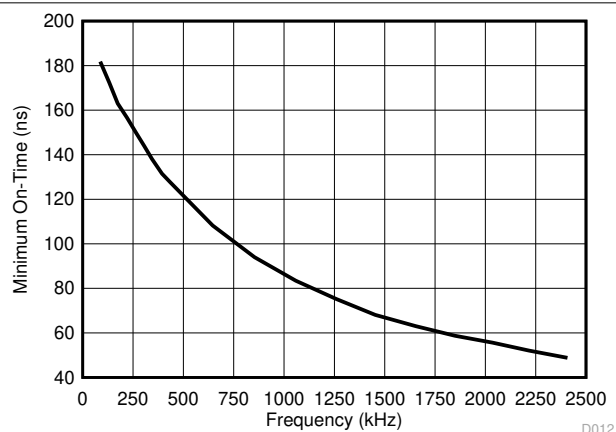


图 8-12.  $t_{\text{ON(MIN)}}$  vs Frequency

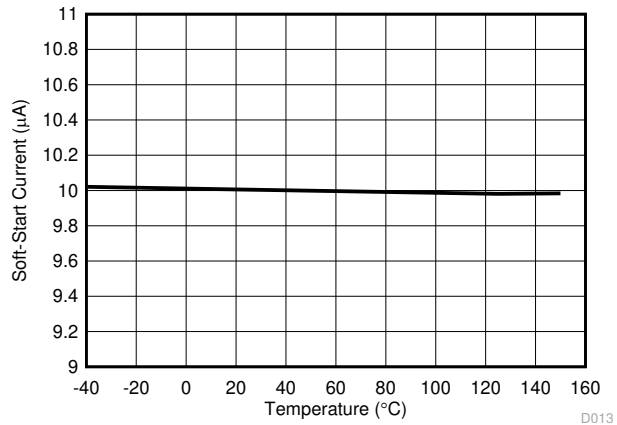


图 8-13.  $I_{SS}$  vs Temperature

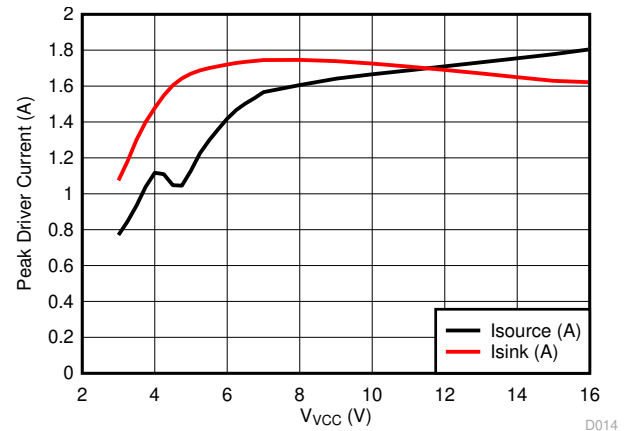


图 8-14. Peak Driver Current vs  $V_{CC}$

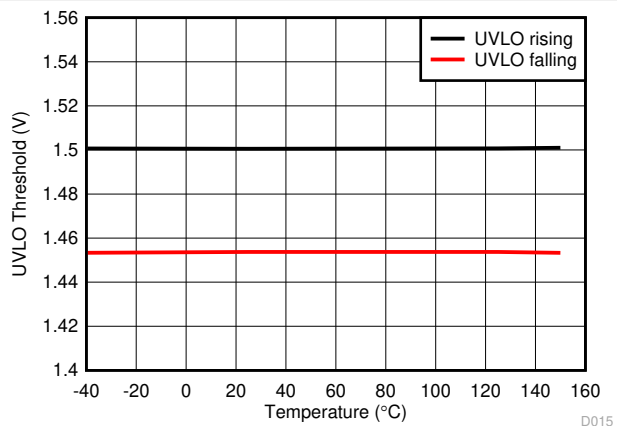


图 8-15. UVLO Threshold vs Temperature

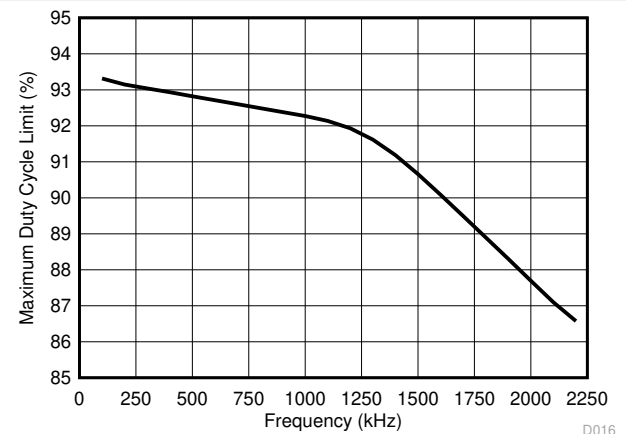


图 8-16. Maximum Duty Cycle vs Frequency



## 9.3 Feature Description

### 9.3.1 Line Undervoltage Lockout (UVLO/SYNC/EN Pin)

The device has a dual-level UVLO circuit. During power-on, if the BIAS pin voltage is greater than 2.7 V, and the UVLO pin voltage is in between the enable threshold ( $V_{EN}$ ) and the UVLO threshold ( $V_{UVLO}$ ) for more than 1.5  $\mu$ s (see § 9.3.6 for more details), the device starts up and an internal configuration starts. The device typically requires a 65- $\mu$ s internal start-up delay before entering standby mode. In standby mode, the VCC regulator and RT regulator are operational, SS pin is grounded, and there is no switching at the GATE output.

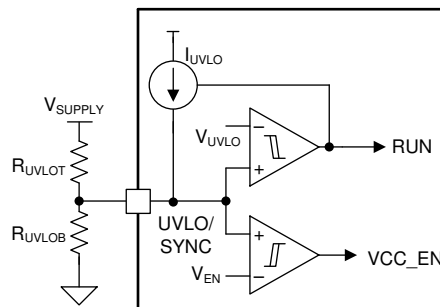


图 9-1. Line UVLO and Enable

When the UVLO pin voltage is above the UVLO threshold, the device enters run mode. In the run mode, a soft-start sequence starts if the VCC voltage is greater than 4.5 V, or 50  $\mu$ s after the VCC voltage exceeds the 2.85-V VCC UV threshold ( $V_{VCC-UVLO}$ ), whichever comes first. UVLO hysteresis is accomplished with an internal 50-mV voltage hysteresis and an additional 5- $\mu$ A current source that is switched on or off. When the UVLO pin voltage exceeds the UVLO threshold, the current source is enabled to quickly raise the voltage at the UVLO pin. When the UVLO pin voltage falls below the UVLO threshold, the current source is disabled, causing the voltage at the UVLO pin to fall quickly. When the UVLO pin voltage is less than the enable threshold ( $V_{EN}$ ), the device enters shutdown mode after a 35- $\mu$ s (typical) delay with all functions disabled.

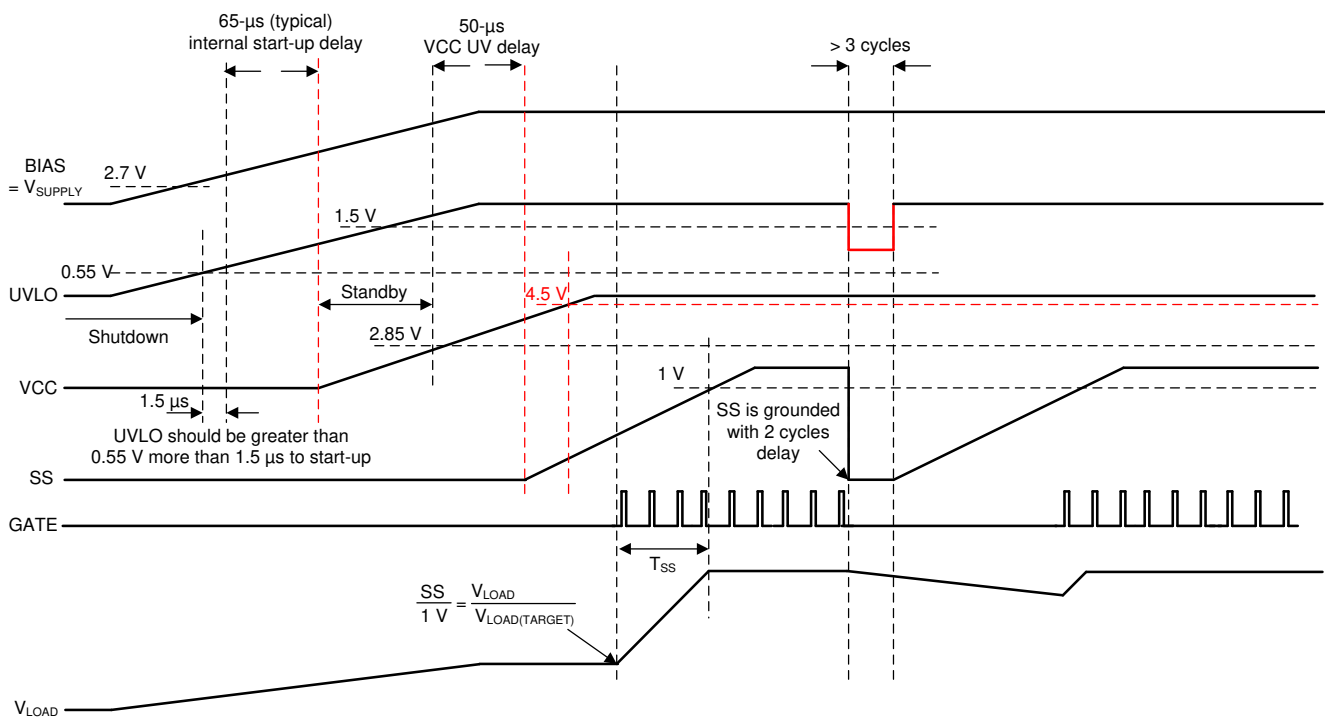


图 9-2. Boost Start-Up Waveforms Case 1: Start-Up by 2.85-V VCC UVLO, UVLO Toggle After Start-Up

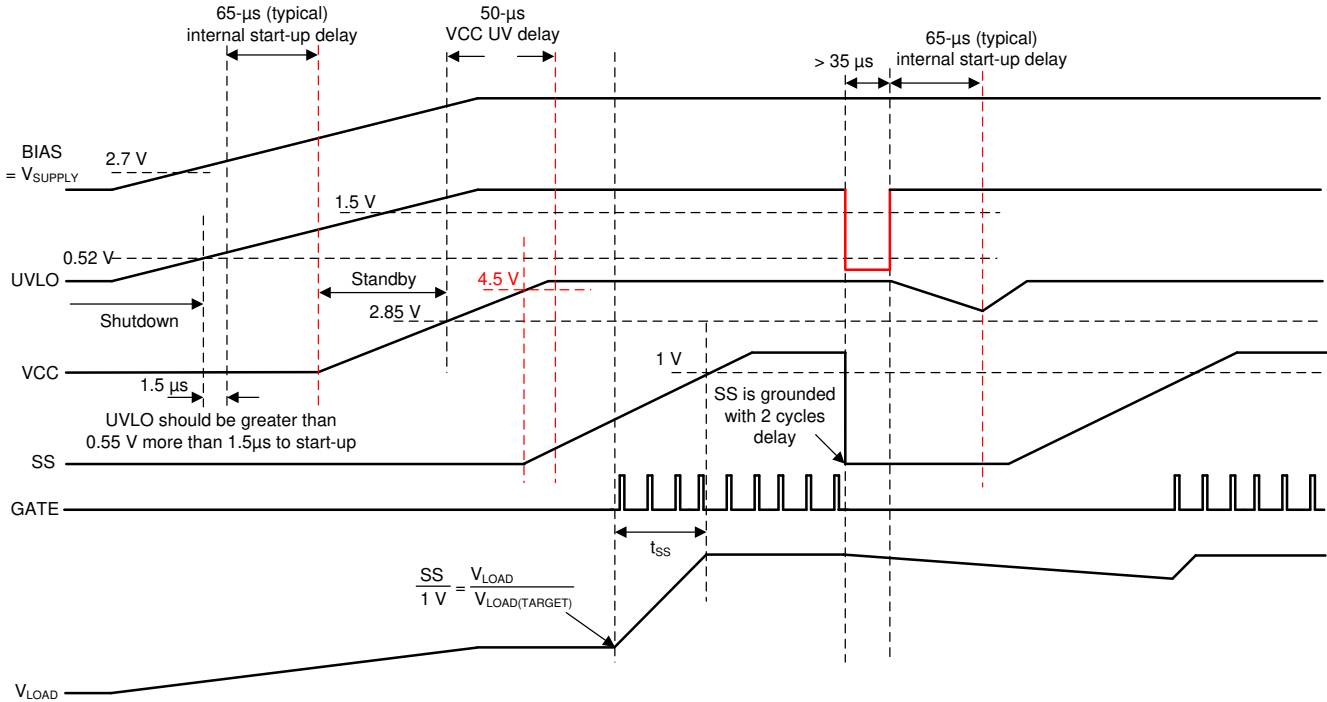


图 9-3. Boost Start-Up Waveforms Case 2: Start-Up When VCC > 4.5 V, EN Toggle After Start-Up

The external UVLO resistor divider must be designed so that the voltage at the UVLO pin is greater than 1.5 V (typical) when the input voltage is in the desired operating range. The values of  $R_{UVLOT}$  and  $R_{UVLOB}$  can be calculated as shown in 方程式 1 and 方程式 2.

$$R_{UVLOT} = \frac{V_{SUPPLY(ON)} \times \frac{V_{UVLO(FALLING)}}{V_{UVLO(RISING)}} - V_{SUPPLY(OFF)}}{I_{UVLO}} \quad (1)$$

where

- $V_{SUPPLY(ON)}$  is the desired start-up voltage of the converter.
- $V_{SUPPLY(OFF)}$  is the desired turnoff voltage of the converter.

$$R_{UVLOB} = \frac{V_{UVLO(RISING)} \times R_{UVLOT}}{V_{SUPPLY(ON)} - V_{UVLO(RISING)}} \quad (2)$$

UVLO capacitor ( $C_{UVLO}$ ) is required in case the input voltage drops below  $V_{SUPPLY(OFF)}$  momentarily during start-up or during a severe load transient at the low input voltage. If the required UVLO capacitor is large, an additional series UVLO resistor ( $R_{UVLOS}$ ) can be used to quickly raise the voltage at the UVLO pin when the 5- $\mu$  A hysteresis current turns on.

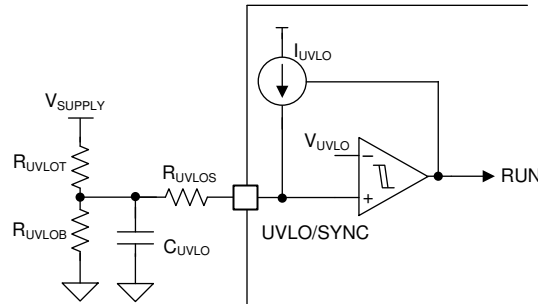


图 9-4. Line UVLO Using Three UVLO Resistors

Do not leave the UVLO pin floating. Connect to the BIAS pin if not used.

### 9.3.2 High Voltage VCC Regulator (BIAS, VCC Pin)

The device has an internal wide input VCC regulator which is sourced from the BIAS pin. The wide input VCC regulator allows the BIAS pin to be connected directly to supply voltages from 3.5 V to 60 V.

The VCC regulator turns on when the device is in the standby or run mode. When the BIAS pin voltage is below the VCC regulation target, the VCC output tracks the BIAS with a small dropout voltage. When the BIAS pin voltage is greater than the VCC regulation target, the VCC regulator provides 6.85-V supply for the N-channel MOSFET driver.

The VCC regulator sources current into the capacitor connected to the VCC pin with a minimum of 35-mA capability. The recommended VCC capacitor value is from 1  $\mu$ F to 4.7  $\mu$ F.

The device supports a wide input range from 3.5 V to 60 V in normal configuration. By connecting the BIAS pin directly to the VCC pin, the device supports inputs from 2.97 V to 16 V. This configuration is recommended when the device starts up from a 1-cell battery.

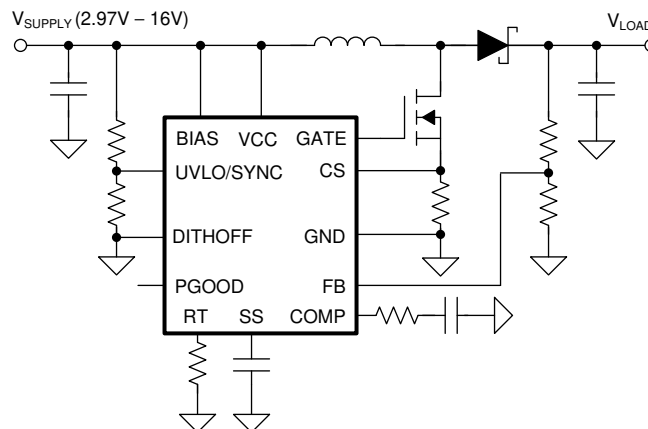
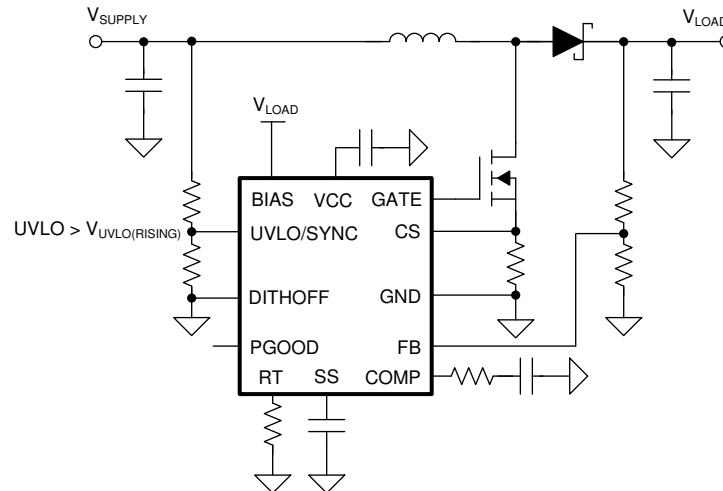


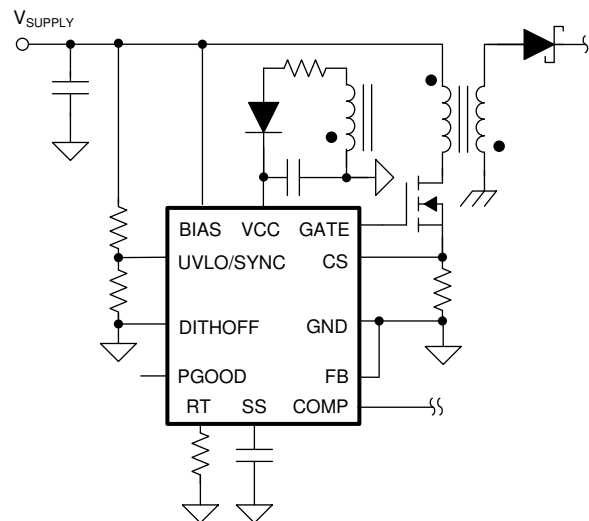
图 9-5. 2.97-V Start-Up (BIAS = VCC)

The minimum supply voltage after start-up can be further decreased by supplying the BIAS pin from the boost converter output or from an external power supply as shown in 图 9-6.



### 图 9-6. Decrease the Minimum Operating Voltage After Start-Up

In flyback topology, the internal power dissipation of the device can be decreased by supplying the VCC using an additional transformer winding. In this configuration, the external VCC supply voltage must be greater than the VCC regulation target ( $V_{VCC-REG}$ ), and the BIAS pin voltage must be greater the VCC voltage because the VCC regulator includes a diode between VCC and BIAS.



**图 9-7. External VCC Supply ( $\text{BIAS} \geq \text{VCC}$ )**

If the voltage of the external VCC bias supply is greater than the BIAS pin voltage, use an external blocking diode from the input power supply to the BIAS pin to prevent the external bias supply from passing current to the boost input supply through VCC.

### 9.3.3 Soft Start (SS Pin)

The soft-start feature helps the converter gradually reach the steady state operating point, thus reducing start-up stresses and surges. The device regulates the FB pin to the SS pin voltage or the internal reference, whichever is lower.

At start-up, the internal 10- $\mu$ A soft-start current source ( $I_{SS}$ ) turns on 50  $\mu$ s after the VCC voltage exceeds the 2.85-VCC UV threshold, or if the VCC voltage is greater than 4.5 V, whichever comes first. The soft-start current gradually increases the voltage on an external soft-start capacitor connected to the SS pin. This results in a gradual rise of the output voltage. The SS pin is pulled down to ground by an internal switch when the VCC is



less than VCC UVLO threshold, the UVLO is less than the UVLO threshold, during hiccup mode off-time or thermal shutdown.

In boost topology, soft-start time ( $t_{SS}$ ) varies with the input supply voltage. The soft-start time in boost topology is calculated as shown in 方程式 3.

$$t_{SS} = \frac{C_{SS}}{I_{SS}} \times \left( 1 - \frac{V_{SUPPLY}}{V_{LOAD}} \right) \quad (3)$$

In SEPIC topology, the soft-start time ( $t_{SS}$ ) is calculated as follows.

$$t_{SS} = \frac{C_{SS}}{I_{SS}} \quad (4)$$

TI recommends choosing soft-start time long enough so that the converter can start up without going into an overcurrent state. See 节 9.3.11 for more detailed information.

图 9-8 shows an implementation of primary side soft start in flyback topology.

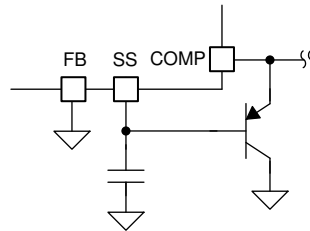


图 9-8. Primary-Side Soft Start in Flyback

图 9-9 shows an implementation of secondary side soft start in flyback topology.

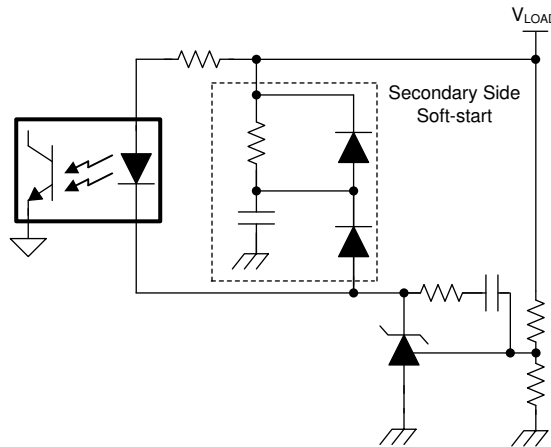


图 9-9. Secondary-Side Soft Start in Flyback

### 9.3.4 Switching Frequency (RT Pin)

The switching frequency of the device can be set by a single RT resistor connected between the RT and the GND pins. The resistor value to set the RT switching frequency ( $f_{RT}$ ) is calculated as shown in 方程式 5.

$$R_T = \frac{2.21 \times 10^{10}}{f_{RT(TYPICAL)}} - 955 \quad (5)$$

The RT pin is regulated to 0.5 V by the internal RT regulator when the device is enabled.

### 9.3.5 Dual Random Spread Spectrum (DRSS)

The device provides a digital spread spectrum which reduces the EMI of the power supply over a wide frequency range. This function is dynamically selectable during operation. The internal modulator dithers the internal clock when the DITHOFF pin is less than 1.0 V or the pin is grounded, and it stops clock dithering when the DITHOFF pin is greater than 2.0 V or the pin is connected to VCC. When an external synchronization clock is applied to the SYNC pin, the internal spread spectrum is disabled. DRSS (a) combines a low-frequency triangular modulation profile (b) with a high frequency cycle-by-cycle random modulation profile (c). The low frequency triangular modulation improves performance in lower radio frequency bands (for example, the AM band), while the high frequency random modulation improves performance in higher radio frequency bands (for example, the FM band). In addition, the frequency of the triangular modulation is further modulated randomly to reduce the likelihood of any audible tones. To minimize output voltage ripple caused by spread spectrum, duty cycle is modified on a cycle-by-cycle basis to maintain a nearly constant duty cycle when dithering is enabled (see Figure 9-10).

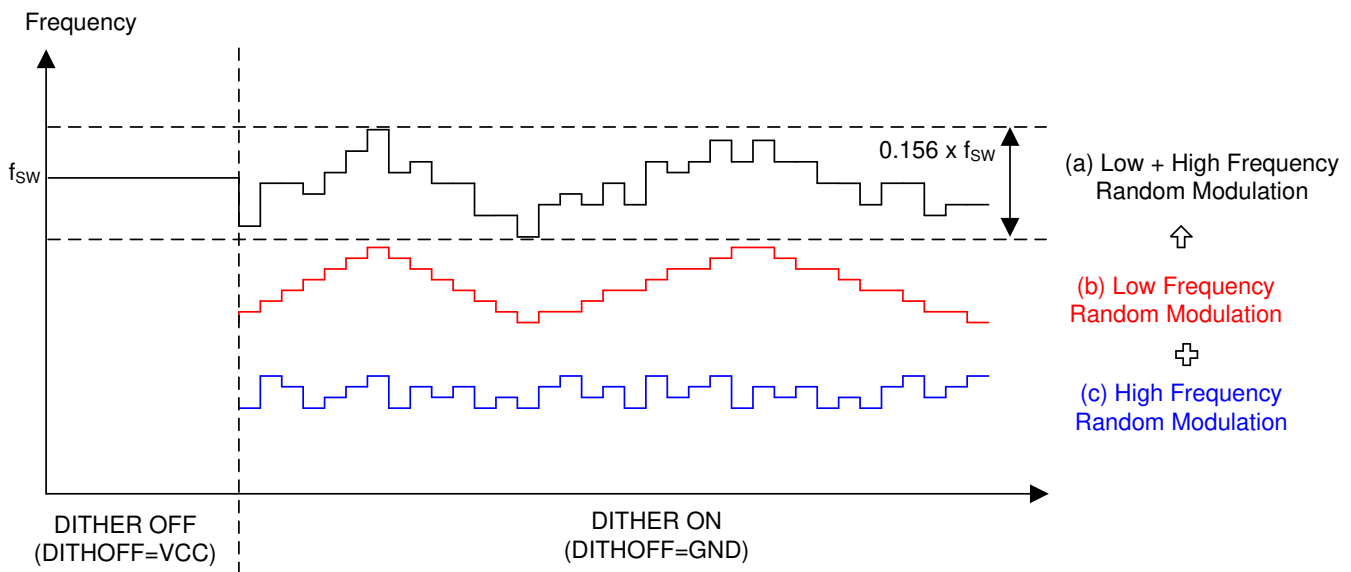
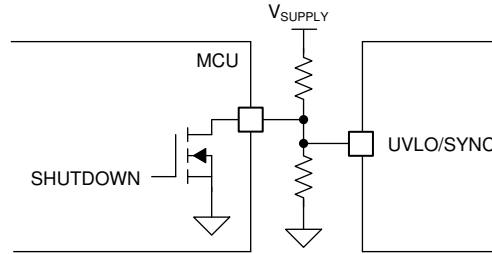


图 9-10. Dual Random Spread Spectrum

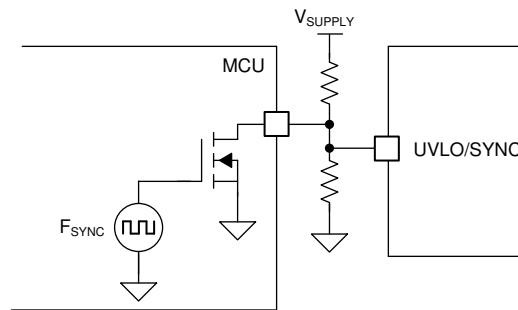
### 9.3.6 Clock Synchronization (UVLO/SYNC/EN Pin)

The switching frequency of the device can be synchronized to an external clock by pulling down the UVLO/SYNC pin. The internal clock of the device is synchronized at the falling edge, but ignores the falling edge input during the forced off-time which is determined by the maximum duty cycle limit. The external synchronization clock must pull down the UVLO/SYNC pin voltage below 1.45 V (typical). The duty cycle of the pulldown pulse is not limited, but the minimum pulldown pulse width must be greater than 150 ns, and the minimum pullup pulse width must be greater than 250 ns. Figure 9-11 shows an implementation of the remote shutdown function. The UVLO pin can be pulled down by a discrete MOSFET or an open-drain output of an MCU. In this configuration, the device stops switching immediately after the UVLO pin is grounded, and the device shuts down 35  $\mu$ s (typical) after the UVLO pin is grounded.



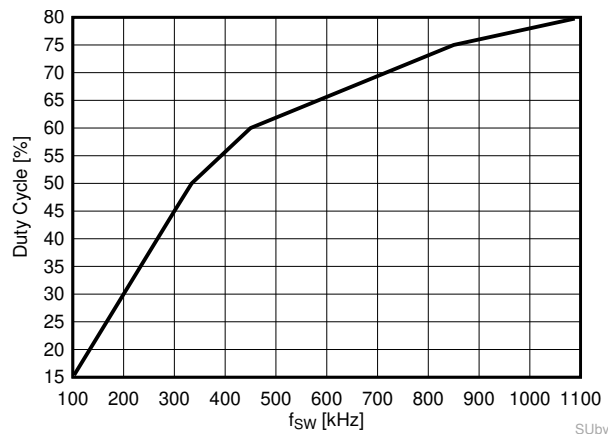
**图 9-11. UVLO and Shutdown**

图 9-12 shows an implementation of shutdown and clock synchronization functions together. In this configuration, the device stops switching immediately when the UVLO pin is grounded, and the device shuts down if  $f_{\text{SYNC}}$  stays in high logic state for longer than 35  $\mu\text{s}$  (typical) (UVLO is in low logic state for more than 35  $\mu\text{s}$  (typical)). The device runs at the  $f_{\text{SYNC}}$  if clock pulses are provided after the device is enabled.

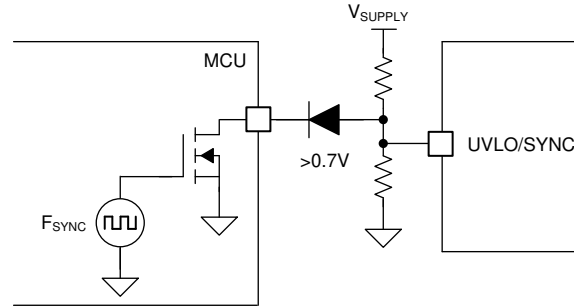


**图 9-12. UVLO, Shutdown, and Clock Synchronization**

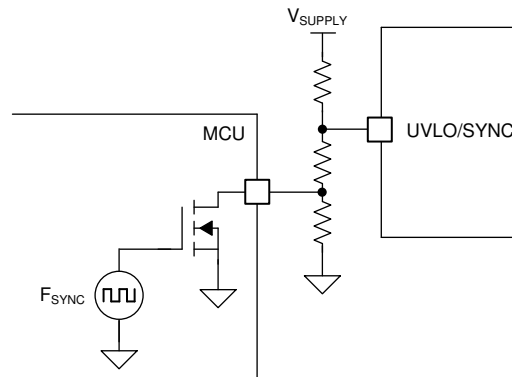
图 9-14 和 图 9-15 show implementations of standby and clock synchronization functions together. In this configuration, the device stops switching immediately if  $f_{\text{SYNC}}$  stays in high logic state and enters standby mode if  $f_{\text{SYNC}}$  stays in high logic state for longer than two switching cycles. The device runs at  $f_{\text{SYNC}}$  if clock pulses are provided. Since the device can be enabled when the UVLO pin voltage is greater than the enable threshold for more than 1.5  $\mu\text{s}$ , the configurations in 图 9-14 and 图 9-15 are recommended if the external clock synchronization pulses are provided from the start before the device is enabled. This 1.5- $\mu\text{s}$  requirement can be relaxed when the duty cycle of the synchronization pulse is greater than 50%. 图 9-13 shows the required minimum duty cycle to start up by synchronization pulses. When the switching frequency is greater than 1.1 MHz, the UVLO pin voltage should be greater than the enable threshold for more than 1.5  $\mu\text{s}$  before applying the external synchronization pulse.



**图 9-13. Required Duty Cycle to Start Up by SYNC**

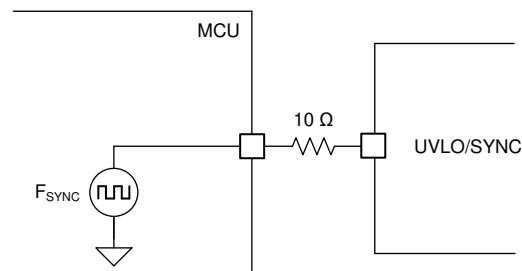


**图 9-14. UVLO, Standby, and Clock Synchronization (a)**



**图 9-15. UVLO, Standby, and Clock Synchronization (b)**

If the UVLO function is not required, the shutdown and clock synchronization functions can be implemented together by using one push-pull output of the MCU. In this configuration, the device shuts down if  $f_{\text{SYNC}}$  stays in low logic state for longer than 35  $\mu\text{s}$  (typical). The device is enabled if  $f_{\text{SYNC}}$  stays in high logic state for longer than 1.5  $\mu\text{s}$ . The device runs at the  $f_{\text{SYNC}}$  if clock pulses are provided after the device is enabled. Also, in this configuration, it is recommended to apply the external clock pulses after the BIAS is supplied. By limiting the current flowing into the UVLO pin below 1 mA using a current limiting resistor, the external clock pulses can be supplied before the BIAS is supplied (see [Figure 9-16](#)).



### 图 9-16. Shutdown and Clock Synchronization

图 9-17 shows an implementation of inverted enable using external circuit.



### 9.3.7 Current Sense and Slope Compensation (CS Pin)

The device can generate the programmable slope compensation ramp using an external slope resistor ( $R_{SL}$ ) and a sawtooth current source with a slope of  $30 \mu A \times f_{RT}$ . This current flows out of the CS pin.



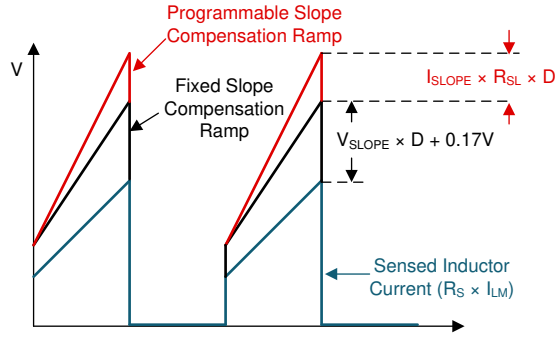


图 9-19. Slope Compensation Ramp (a) at PWM Comparator Input

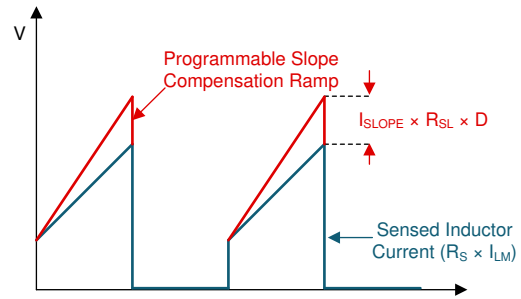


图 9-20. Slope Compensation Ramp (b) at Current Limit Comparator Input

Use 方程式 6 to calculate the value of the peak slope current ( $I_{SLOPE}$ ) and use 方程式 7 to calculate the value of the peak slope voltage ( $V_{SLOPE}$ ).

$$I_{SLOPE} = 30\mu A \times \frac{f_{RT}}{f_{SYNC}} \quad (6)$$

$$V_{SLOPE} = 40mV \times \frac{f_{RT}}{f_{SYNC}} \quad (7)$$

where

- $f_{SYNC} = f_{RT}$  if clock synchronization is not used.

According to peak current mode control theory, the slope of the compensation ramp must be greater than half of the sensed inductor current falling slope to prevent subharmonic oscillation at high duty cycle. Therefore, the minimum amount of slope compensation in boost topology should satisfy the following inequality:

$$0.5 \times \frac{(V_{LOAD} + V_F) - V_{SUPPLY}}{L_M} \times R_S \times \text{Margin} < 40mV \times f_{SW} \quad (8)$$

where

- $V_F$  is a forward voltage drop of D1, the external diode

The recommended margin to cover non-ideal factors is 1.2. If required,  $R_{SL}$  can be added to further increase the slope of the compensation ramp. Typically 82% of the sensed inductor current falling slope is known as an optimal amount of the slope compensation. The  $R_{SL}$  value to achieve 82% of the sensed inductor current falling slope is calculated as shown in 方程式 9.

$$0.82 \times \frac{(V_{LOAD} + V_F) - V_{SUPPLY}}{L_M} \times R_S = (30\mu A \times R_{SL} + 40mV) \times f_{SW} \quad (9)$$

If clock synchronization is not used, the  $f_{SW}$  frequency equals the  $f_{RT}$  frequency. If clock synchronization is used, the  $f_{SW}$  frequency equals the  $f_{SYNC}$  frequency. The maximum value for the  $R_{SL}$  resistance is 2 k $\Omega$ .

### 9.3.8 Current Limit and Minimum On-time (CS Pin)

The device provides cycle-by-cycle peak current limit protection that turns off the MOSFET when the sum of the inductor current and the programmable slope compensation ramp reaches the current limit threshold ( $V_{CLTH}$ ). Peak inductor current limit ( $I_{PEAK-CL}$ ) in steady state is calculated as shown in [方程式 10](#).

$$I_{PEAK-CL} = \frac{V_{CLTH} - 30\mu A \times R_{SL} \times \frac{f_{RT}}{f_{SYNC}} \times D}{R_S} \quad (10)$$

The practical duty cycle is greater than the estimated due to voltage drops across the MOSFET and sense resistor. The estimated duty cycle is calculated as shown in [方程式 11](#).

$$D = 1 - \frac{V_{SUPPLY}}{V_{LOAD} + V_F} \quad (11)$$

Boost converters have a natural pass-through path from the supply to the load through the high-side power diode (D1). Because of this path and the minimum on-time limitation of the device, boost converters cannot provide current limit protection when the output voltage is close to or less than the input supply voltage. The minimum on-time is shown in [图 8-12](#) and is calculated as [方程式 12](#).

$$t_{ON(MIN)} \approx \frac{800 \times 10^{-15}}{\frac{1}{8 \times R_T} + 4 \times 10^{-6}} \quad (12)$$

If required, a small external RC filter ( $R_F$ ,  $C_F$ ) at the CS pin can be added to overcome the large leading edge spike of the current sense signal. Select an  $R_F$  value in the range of 10  $\Omega$  to 200  $\Omega$  and a  $C_F$  value in the range of 100 pF to 2 nF. Because of the effect of this RC filter, the peak current limit is not valid when the on-time is less than  $2 \times R_F \times C_F$ . To fully discharge the  $C_F$  during the off-time, the RC time constant should satisfy the following inequality.

$$3 \times R_F \times C_F < \frac{1-D}{f_{SW}} \quad (13)$$

### 9.3.9 Feedback and Error Amplifier (FB, COMP Pin)

The feedback resistor divider is connected to an internal transconductance error amplifier which features high output resistance ( $R_O = 10 \text{ M}\Omega$ ) and wide bandwidth ( $BW = 7 \text{ MHz}$ ). The internal transconductance error amplifier sources current, which is proportional to the difference between the FB pin and the SS pin voltage or the internal reference, whichever is lower. The internal transconductance error amplifier provides symmetrical sourcing and sinking capability during normal operation and reduces its sinking capability when the FB is greater than OVP threshold.

To set the output regulation target, select the feedback resistor values as shown in [方程式 14](#).

$$V_{LOAD} = V_{REF} \times \left( \frac{R_{FBT}}{R_{FBB}} + 1 \right) \quad (14)$$

The output of the error amplifier is connected to the COMP pin, allowing the use of a Type 2 loop compensation network.  $R_{COMP}$ ,  $C_{COMP}$ , and optional  $C_{HF}$  loop compensation components configure the error amplifier gain and phase characteristics to achieve a stable loop response. The absolute maximum voltage rating of the FB pin is

3.8 V. If necessary, especially during automotive load dump transient, the feedback resistor divider input can be clamped with an external zener diode.

The COMP pin features internal clamps. The maximum COMP clamp limits the maximum COMP pin voltage below its absolute maximum rating even in shutdown. The minimum COMP clamp limits the minimum COMP pin voltage in order to start switching as soon as possible during no load to heavy load transition. The minimum COMP clamp is disabled when FB is connected to ground in flyback topology.

### 9.3.10 Power-Good Indicator (PGOOD pin)

The device has a power-good indicator (PGOOD) to simplify sequencing and supervision. The PGOOD switches to a high impedance open-drain state when the FB pin voltage is greater than the feedback under voltage threshold ( $V_{UVTH}$ ), the VCC is greater than the VCC UVLO threshold and the UVLO/EN is greater than the EN threshold. A 25- $\mu$ s deglitch filter prevents any false pulldown of the PGOOD due to transients. The recommended minimum pullup resistor value is 10 k $\Omega$ .

Due to the internal diode path from the PGOOD pin to the BIAS pin, the PGOOD pin voltage cannot be greater than  $V_{BIAS} + 0.3$  V.

### 9.3.11 Hiccup Mode Overload Protection (LM51561 Only)

To further protect the converter during prolonged current limit conditions, the LM51561 device option provides a hiccup mode overload protection. The internal hiccup mode fault timer of the device counts the PWM clock cycles when the cycle-by-cycle current limiting occurs after soft start is finished. When the hiccup mode fault timer detects 64 cycles of current limiting, an internal hiccup mode off-timer forces the device to stop switching and pulls down SS. Then, the device will restart after 32 768 cycles of hiccup mode off-time. The 64-cycle hiccup mode fault timer is reset if eight consecutive switching cycles occur without exceeding the current limit threshold. The soft-start time must be long enough not to trigger the hiccup mode protection after the soft start is finished.

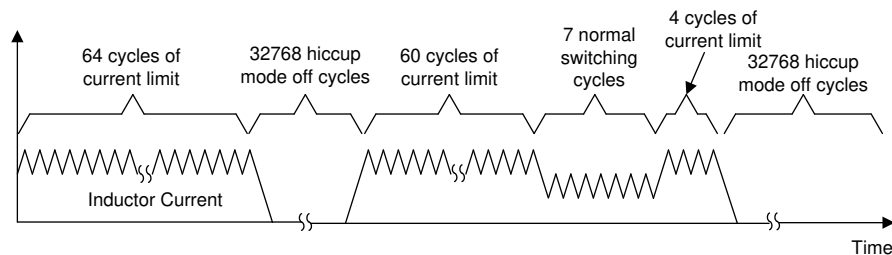


图 9-21. Hiccup Mode Overload Protection

To avoid an unexpected hiccup mode operation during a harsh load transient condition, it is recommended to have more margin when programming the peak-current limit.

### 9.3.12 Maximum Duty Cycle Limit and Minimum Input Supply Voltage

When designing boost converters, the maximum duty cycle should be reviewed at the minimum supply voltage. The minimum input supply voltage that can achieve the target output voltage is limited by the maximum duty cycle limit, and it can be estimated as follows.

$$V_{\text{SUPPLY(MIN)}} \approx (V_{\text{LOAD}} + V_F) \times (1 - D_{\text{MAX}}) + I_{\text{SUPPLY(MAX)}} \times R_{\text{DCR}} + I_{\text{SUPPLY(MAX)}} \times (R_{\text{DS(ON)}} + R_S) \times D_{\text{MAX}} \quad (15)$$

where

- $I_{\text{SUPPLY(MAX)}}$  is the maximum input current
- $R_{\text{DCR}}$  is the DC resistance of the inductor
- $R_{\text{DS(ON)}}$  is the on-resistance of the MOSFET



$$D_{MAX1} = 1 - 0.1 \times \frac{f_{SYNC}}{f_{RT}} \quad (16)$$

$$D_{MAX2} = 1 - 100ns \times f_{SW} \quad (17)$$

The minimum input supply voltage can be further decreased by supplying  $f_{SYNC}$ , which is less than  $f_{RT}$ .  $D_{MAX}$  is  $D_{MAX1}$  or  $D_{MAX2}$ , whichever is lower.

### 9.3.13 MOSFET Driver (GATE Pin)

The device provides an N-channel MOSFET driver that can source or sink a peak current of 1.5 A. The peak sourcing current is larger when supplying an external VCC that is higher than 6.75 V VCC regulation target. During start-up, especially when the input voltage range is below the VCC regulation target, the VCC voltage must be sufficient to completely enhance the MOSFET. If the MOSFET drive voltage is lower than the MOSFET gate plateau voltage during start-up, the boost converter may not start up properly and it can stick at the maximum duty cycle in a high power dissipation state. This condition can be avoided by selecting a lower threshold N-channel MOSFET switch and setting the  $V_{SUPPLY(ON)}$  greater than 6 to 7 V. Because the internal VCC regulator has a limited sourcing capability, the MOSFET gate charge should satisfy the following inequality.

$$Q_{G@VCC} \times f_{SW} < 35mA \quad (18)$$

An internal 1-M $\Omega$  resistor is connected between GATE and GND to prevent a false turnon during shutdown. In boost topology, switch node dV/dT must be limited during the 65- $\mu$ s internal start-up delay to avoid a false turnon, which is caused by the coupling through  $C_{DG}$  parasitic capacitance of the MOSFET.

### 9.3.14 Overvoltage Protection (OVP)

The device has OVP for the output voltage. OVP is sensed at the FB pin. If the voltage at the FB pin rises above the overvoltage threshold ( $V_{OVTH}$ ), OVP is triggered and switching stops. During OVP, the internal error amplifier is operational, but the maximum source and sink capability is decreased to 40  $\mu$ A.

### 9.3.15 Thermal Shutdown (TSD)

An internal thermal shutdown turns off the VCC regulator, disables switching, and pulls down the SS when the junction temperature exceeds the thermal shutdown threshold ( $T_{TSD}$ ). After the temperature is decreased by 15°C, the VCC regulator is enabled again and the device performs a soft start.

## 9.4 Device Functional Modes

### 9.4.1 Shutdown Mode

If the UVLO pin voltage is below the enable threshold for longer than 35  $\mu$ s (typical), the device goes to the shutdown mode with all functions disabled. In shutdown mode, the device decreases the BIAS pin current consumption to below 2.6  $\mu$ A (typical)

### 9.4.2 Standby Mode

If the UVLO pin voltage is greater than the enable threshold and below the UVLO threshold for longer than 1.5  $\mu$ s, the device is in standby mode with the VCC regulator operational, RT regulator operational, SS pin grounded, and no switching at the GATE output. The PGOOD is activated when the VCC voltage is greater than the VCC UV threshold.

### 9.4.3 Run Mode

If the UVLO pin voltage is above the UVLO threshold and the VCC voltage is sufficient, the device enters RUN mode. In this mode, soft start starts 50  $\mu$ s after the VCC voltage exceeds the 2.85 VCC UV threshold, or if the VCC voltage is greater than 4.5 V, whichever comes first.

## 10 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 10.1 Application Information

[How to Design a Boost Converter Using LM5156x](#) explains how to design boost, SEPIC, and Flyback converters using the device. This comprehensive application note includes component selections and loop response optimization.

### 10.2 Typical Application

图 10-1 shows all optional components to design a boost converter.

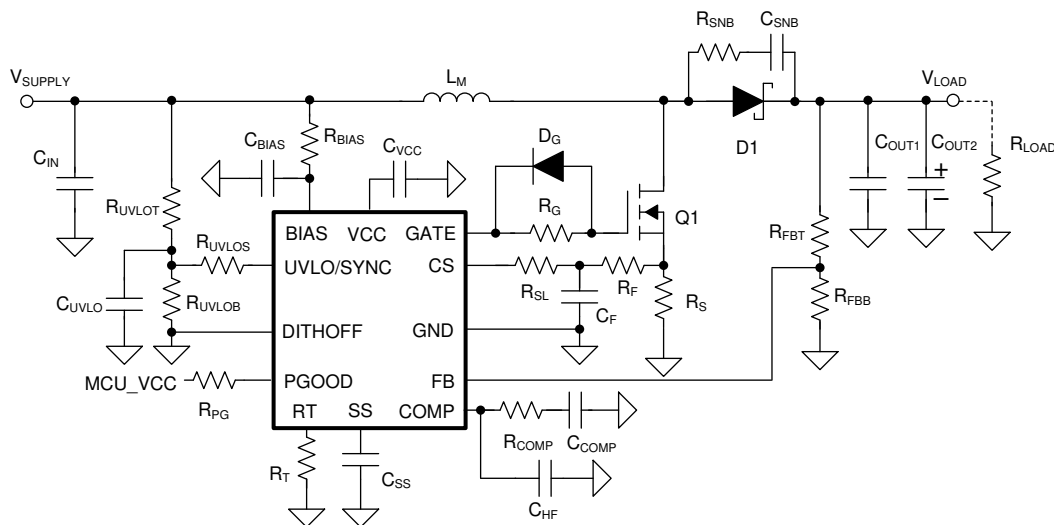


图 10-1. Typical Boost Converter Circuit With Optional Components

#### 10.2.1 Design Requirements

表 10-1 shows the intended input, output, and performance parameters for this application example.

表 10-1. Design Example Parameters

DESIGN PARAMETER	VALUE
Minimum input supply voltage ( $V_{SUPPLY(MIN)}$ )	6 V
Target output voltage ( $V_{LOAD}$ )	24 V
Maximum load current ( $I_{LOAD}$ )	2 A ( $\approx 48$ Watt)
Typical switching frequency ( $f_{SW}$ )	440 kHz

#### 10.2.2 Detailed Design Procedure

Use the [LM5155x / LM5156x Boost Quick Start Calculator](#) to expedite the process of designing of a regulator for a given application based on the LM5156x device.

The LM5156x device is also WEBENCH® Designer enabled. The WEBENCH software uses an iterative design procedure and accesses comprehensive data bases of components when generating a design.

### 10.2.2.1 Custom Design With WEBENCH® Tools

Click [here](#) to create a custom design using the LM5156x device with the WEBENCH® Power Designer.

1. Start by entering the input voltage ( $V_{IN}$ ), output voltage ( $V_{OUT}$ ), and output current ( $I_{OUT}$ ) requirements.
2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at [www.ti.com/WEBENCH](http://www.ti.com/WEBENCH).

### 10.2.2.2 Recommended Components

表 10-2 shows a recommended list of materials for this typical application.

表 10-2. List of Materials<sup>(1)</sup>

REFERENCE DESIGNATOR	QTY.	SPECIFICATION	MANUFACTURER	PART NUMBER
R <sub>T</sub>	1	RES, 49.9 k, 1%, 0.1 W, AEC-Q200 Grade 0, 0603	Vishay-Dale	CRCW060349K9FKEA
R <sub>FBT</sub>	1	RES, 47.0 k, 1%, 0.1 W, AEC-Q200 Grade 0, 0603	Vishay-Dale	CRCW060347K0FKEA
R <sub>FBB</sub>	1	RES, 2.0 k, 5%, 0.1 W, AEC-Q200 Grade 0, 0603	Vishay-Dale	CRCW06032K00JNEA
L <sub>M</sub>	1	Inductor, Shielded, Composite, 6.8 $\mu$ H, 18.5 A, 0.01 $\Omega$ , SMD	Coilcraft	XAL1010-682MEB
R <sub>S</sub>	1	RES, 0.008, 1%, 3 W, AEC-Q200 Grade 0, 2512 WIDE	Susumu	KRL6432E-M-R008-F-T1
R <sub>SL</sub>	1	RES, 0, 5%, 0.1 W, 0603	Yageo America	RC0603JR-070RL
C <sub>OUT1</sub>	3	CAP, CERM, 4.7 $\mu$ F, 50 V, $\pm$ 10%, X7R, 1210	TDK	C3225X7R1H475K250AB
C <sub>OUT2</sub> (Bulk)	2	CAP, Aluminum Polymer, 100 $\mu$ F, 50 V, $\pm$ 20%, 0.025 $\Omega$ , AEC-Q200 Grade 2, D10xL10mm SMD	Chemi-Con	HHXB500ARA101MJA0G
C <sub>IN1</sub>	6	CAP, CERM, 10 $\mu$ F, 50 V, $\pm$ 10%, X7R, 1210	MuRata	GRM32ER71H106KA12L
C <sub>IN2</sub> (Bulk)	1	CAP, Polymer Hybrid, 100 $\mu$ F, 50 V, $\pm$ 20%, 28 $\Omega$ , 10x10 SMD	Panasonic	EEH2C1H101P
Q1	1	MOSFET, N-CH, 40 V, 50 A, AEC-Q101, SON-8	Infineon	IPC50N04S5L5R5ATMA1
D1	1	Schottky, 60 V, 10 A, AEC-Q101, CFP15	Nexperia	PMEG060V100EPDZ
R <sub>COMP</sub>	1	RES, 11.3 k, 1%, 0.1 W, AEC-Q200 Grade 0, 0603	Vishay-Dale	CRCW060311K3FKEA
C <sub>COMP</sub>	1	CAP, CERM, 0.022 $\mu$ F, 100 V, $\pm$ 10%, X7R, AEC-Q200 Grade 1, 0603	TDK	CGA3E2X7R2A223K080AA
C <sub>HF</sub>	1	CAP, CERM, 220 pF, 20 V, $\pm$ 5%, C0G/NP0, AEC-Q200 Grade 1, 0603	TDK	CGA3E2C0G1H221J080AA
R <sub>UVLOT</sub>	1	RES, 21.0 k, 1%, 0.1 W, AEC-Q200 Grade 0, 0603	Vishay-Dale	CRCW060321K0FKEA
R <sub>UVLOB</sub>	1	RES, 7.32 k, 1%, 0.1 W, AEC-Q200 Grade 0, 0603	Vishay-Dale	CRCW06037K32FKEA
R <sub>UVLOS</sub>	0	N/A	N/A	N/A
C <sub>SS</sub>	1	CAP, CERM, 0.22 $\mu$ F, 50 V, $\pm$ 10%, X7R, AEC-Q200 Grade 1, 0603	TDK	CGA3E3X7R1H224K080AB
D <sub>G</sub>	0	N/A	N/A	N/A
R <sub>G</sub>	1	RES, 0, 5%, 0.1 W, 0603	Yageo America	RC0603JR-070RL
C <sub>F</sub>	1	CAP, CERM, 100 pF, 50 V, $\pm$ 1%, C0G/NP0, 0603	Kemet	C0603C101F5GACTU
R <sub>F</sub>	1	RES, 100, 1%, 0.1 W, 0603	Yageo America	RC0603FR-07100RL

表 10-2. List of Materials<sup>(1)</sup> (continued)

REFERENCE DESIGNATOR	QTY.	SPECIFICATION	MANUFACTURER	PART NUMBER
R <sub>SNB</sub>	0	N/A	N/A	N/A
C <sub>SNB</sub>	0	N/A	N/A	N/A
R <sub>BIAS</sub>	1	RES, 0, 5%, 0.1 W, AEC-Q200 Grade 0, 0603	Panasonic	ERJ-3GEY0R00V
C <sub>BIAS</sub>	1	CAP, CERM, 0.01 $\mu$ F, 50 V, $\pm$ 10%, X7R, 0603	Samsung Electro-Mechanics	CL10B103KB8NCNC
C <sub>VCC</sub>	1	CAP, CERM, 1 $\mu$ F, 16 V, $\pm$ 20%, X7R, AEC-Q200 Grade 1, 0603	MuRata	GCM188R71C105MA64D
R <sub>PG</sub>	1	RES, 24.9 k, 1%, 0.1 W, 0603	Yageo America	RC0603FR-0724K9L

(1) See [Third-party Products Disclaimer](#)

### 10.2.2.3 Inductor Selection ( $L_M$ )

When selecting the inductor, consider three key parameters: inductor current ripple ratio (RR), falling slope of the inductor current, and RHP zero frequency ( $f_{RHP}$ ).

Inductor current ripple ratio is selected to have a balance between core loss and copper loss. The falling slope of the inductor current must be low enough to prevent subharmonic oscillation at high duty cycle (additional  $R_{SL}$  resistor is required if not). Higher  $f_{RHP}$  (= lower inductance) allows a higher crossover frequency and is always preferred when using a small value output capacitor.

The inductance value can be selected to set the inductor current ripple between 30% and 70% of the average inductor current as a good compromise between RR,  $f_{RHP}$ , and inductor falling slope.

### 10.2.2.4 Output Capacitor ( $C_{OUT}$ )

There are a few ways to select the proper value of output capacitor ( $C_{OUT}$ ). The output capacitor value can be selected based on output voltage ripple, output overshoot, or undershoot due to load transient.

The ripple current rating of the output capacitors must be enough to handle the output ripple current. By using multiple output capacitors, the ripple current can be split. In practice, ceramic capacitors are placed closer to the diode and the MOSFET than the bulk aluminum capacitors to absorb the majority of the ripple current.

### 10.2.2.5 Input Capacitor

The input capacitors decrease the input voltage ripple. The required input capacitor value is a function of the impedance of the source power supply. More input capacitors are required if the impedance of the source power supply is not low enough.

### 10.2.2.6 MOSFET Selection

The MOSFET gate driver of the device is sourced from VCC. The maximum gate charge is limited by the 35-mA VCC sourcing current limit.

A leadless package is preferred for high switching-frequency designs. The MOSFET gate capacitance should be small enough so that the gate voltage is fully discharged during the off-time.

### 10.2.2.7 Diode Selection

A Schottky is the preferred type for D1 diode due to its low forward voltage drop and small reverse recovery charge. Low reverse leakage current is an important parameter when selecting the Schottky diode. The diode must be rated to handle the maximum output voltage plus any switching node ringing. Also, it must be able to handle the average output current.

### 10.2.2.8 Efficiency Estimation

The total loss of the boost converter ( $P_{TOTAL}$ ) can be expressed as the sum of the losses in the device ( $P_{IC}$ ), MOSFET power losses ( $P_Q$ ), diode power losses ( $P_D$ ), inductor power losses ( $P_L$ ), and the loss in the sense resistor ( $P_{RS}$ ).

$$P_{TOTAL} = P_{IC} + P_Q + P_D + P_L + P_{RS} \quad (19)$$

$P_{IC}$  can be separated into gate driving loss ( $P_G$ ) and the losses caused by quiescent current ( $P_{IQ}$ ).

$$P_{IC} = P_G + P_{IQ} \quad (20)$$

Each power loss is approximately calculated as follows:

$$P_G = Q_{G(@VCC)} \times V_{BIAS} \times f_{SW} \quad (21)$$

$$P_{IQ} = V_{BIAS} \times I_{BIAS} \quad (22)$$

$I_{VIN}$  and  $I_{VOUT}$  values in each mode can be found in the supply current section of [§ 8.5](#).

$P_Q$  can be separated into switching loss ( $P_{Q(SW)}$ ) and conduction loss ( $P_{Q(COND)}$ ).

$$P_Q = P_{Q(SW)} + P_{Q(COND)} \quad (23)$$

Each power loss is approximately calculated as follows:

$$P_{Q(SW)} = 0.5 \times (V_{LOAD} + V_F) \times I_{SUPPLY} \times (t_R + t_F) \times f_{SW} \quad (24)$$

$t_R$  and  $t_F$  are the rise and fall times of the low-side N-channel MOSFET device.  $I_{SUPPLY}$  is the input supply current of the boost converter.

$$P_{Q(COND)} = D \times I_{SUPPLY}^2 \times R_{DS(ON)} \quad (25)$$

$R_{DS(ON)}$  is the on-resistance of the MOSFET and is specified in the MOSFET data sheet. Consider the  $R_{DS(ON)}$  increase due to self-heating.

$P_D$  can be separated into diode conduction loss ( $P_{VF}$ ) and reverse recovery loss ( $P_{RR}$ ).

$$P_D = P_{VF} + P_{RR} \quad (26)$$

Each power loss is approximately calculated as follows:

$$P_{VF} = (1 - D) \times V_F \times I_{SUPPLY} \quad (27)$$

$$P_{RR} = V_{LOAD} \times Q_{RR} \times f_{SW} \quad (28)$$

$Q_{RR}$  is the reverse recovery charge of the diode and is specified in the diode data sheet. Reverse recovery characteristics of the diode strongly affect efficiency, especially when the output voltage is high.

$P_L$  is the sum of DCR loss ( $P_{DCR}$ ) and AC core loss ( $P_{AC}$ ). DCR is the DC resistance of inductor which is mentioned in the inductor data sheet.

$$P_L = P_{DCR} + P_{AC} \quad (29)$$

Each power loss is approximately calculated as follows:

$$P_{DCR} = I_{SUPPLY}^2 \times R_{DCR} \quad (30)$$

$$P_{AC} = K \times \Delta I^\beta \times f_{SW}^\alpha \quad (31)$$

$$\Delta I = \frac{V_{SUPPLY} \times D \times \frac{1}{f_{SW}}}{L_M} \quad (32)$$

$\Delta I$  is the peak-to-peak inductor current ripple.  $K$ ,  $\alpha$ , and  $\beta$  are core dependent factors which can be provided by the inductor manufacturer.

$P_{RS}$  is calculated as follows:

$$P_{RS} = D \times I_{SUPPLY}^2 \times R_S \quad (33)$$

Efficiency of the power converter can be estimated as follows:

$$\text{Efficiency} = \frac{V_{LOAD} \times I_{LOAD}}{P_{TOTAL} + V_{LOAD} \times I_{LOAD}} \quad (34)$$

### 10.2.3 Application Curve

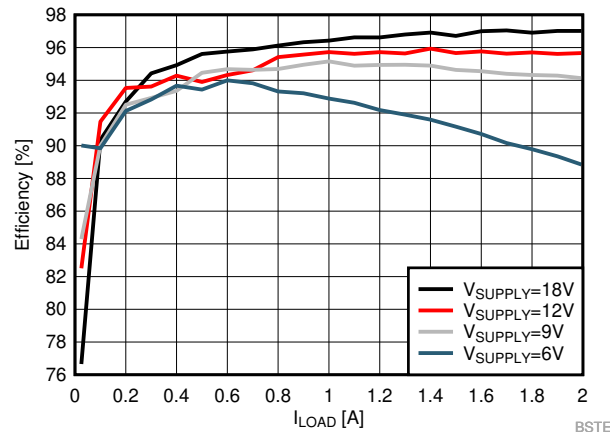


图 10-2. Efficiency

## 10.3 System Examples

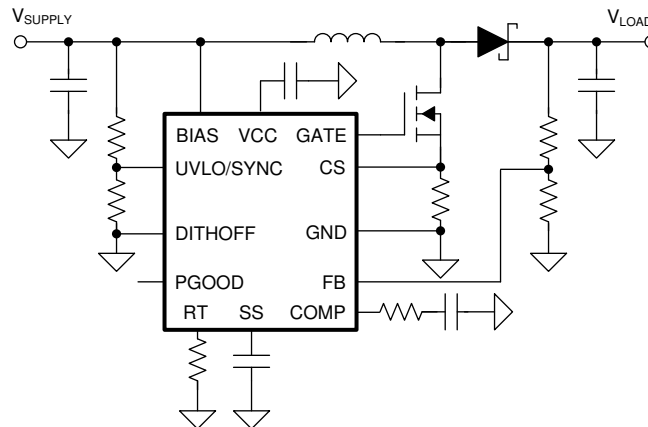


图 10-3. Typical Boost Application

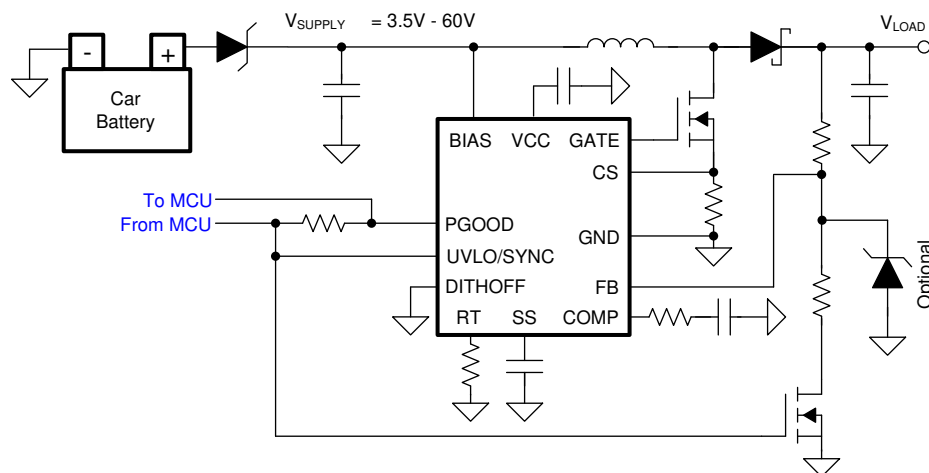


图 10-4. Typical Start-Stop Application

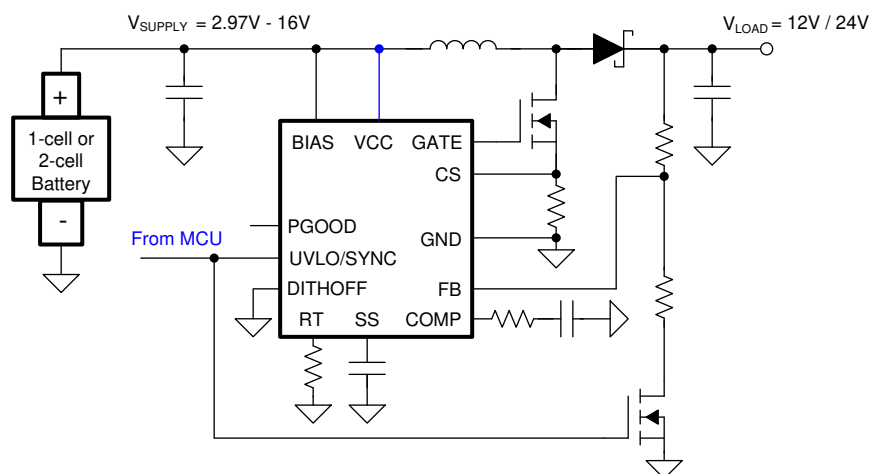


图 10-5. Emergency-call / Boost On-Demand / Portable Speaker

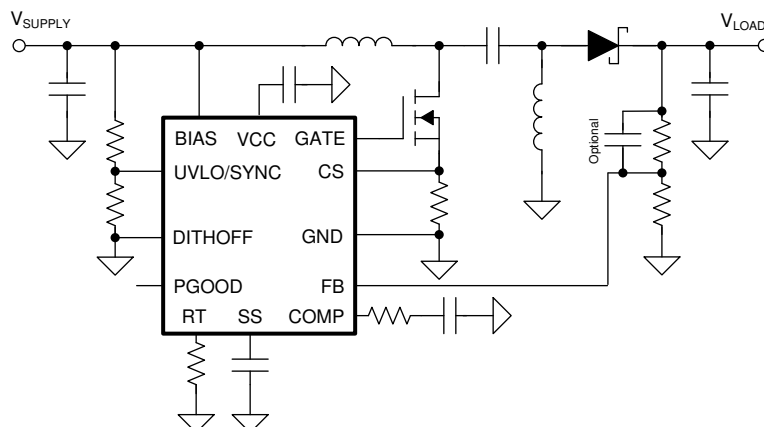


图 10-6. Typical SEPIC Application

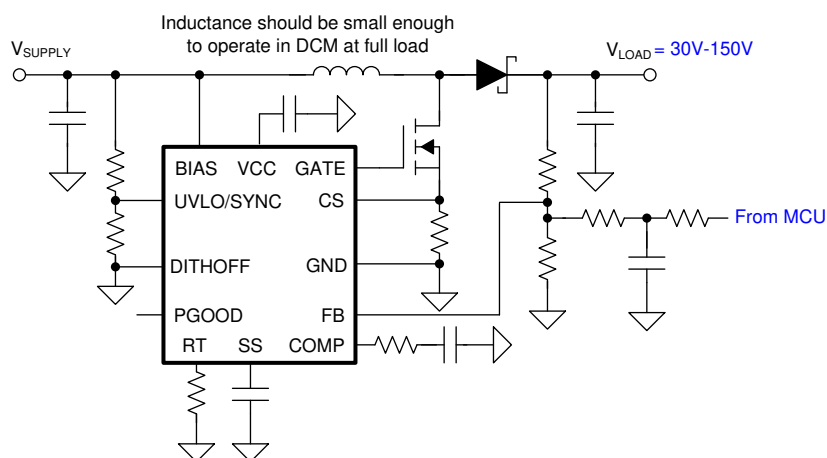


图 10-7. LIDAR Bias Supply 1

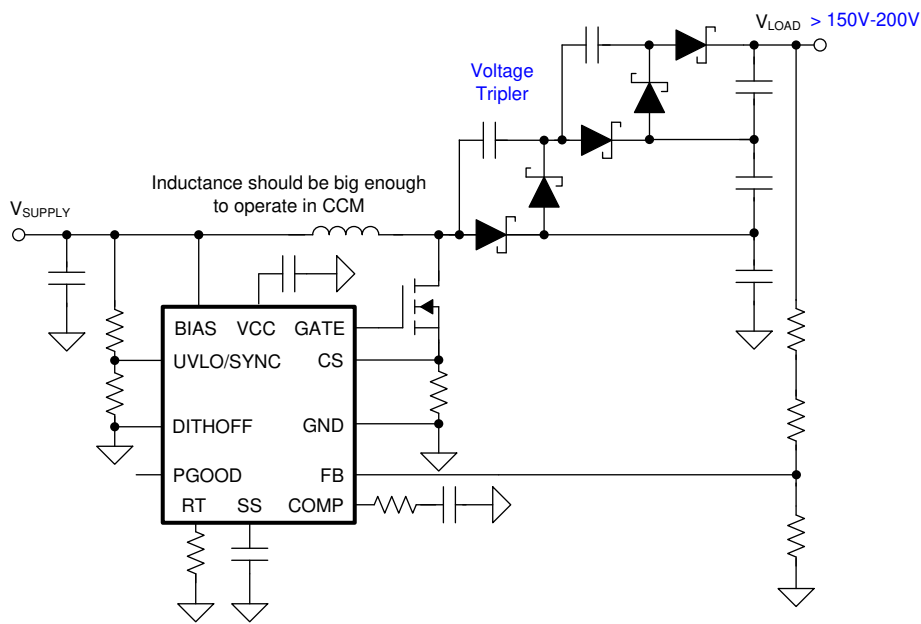


图 10-8. LIDAR Bias Supply 2



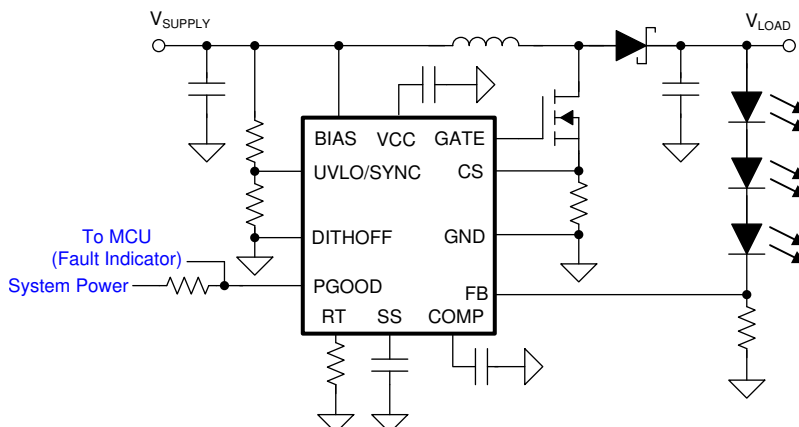


图 10-9. Low-Cost LED Driver

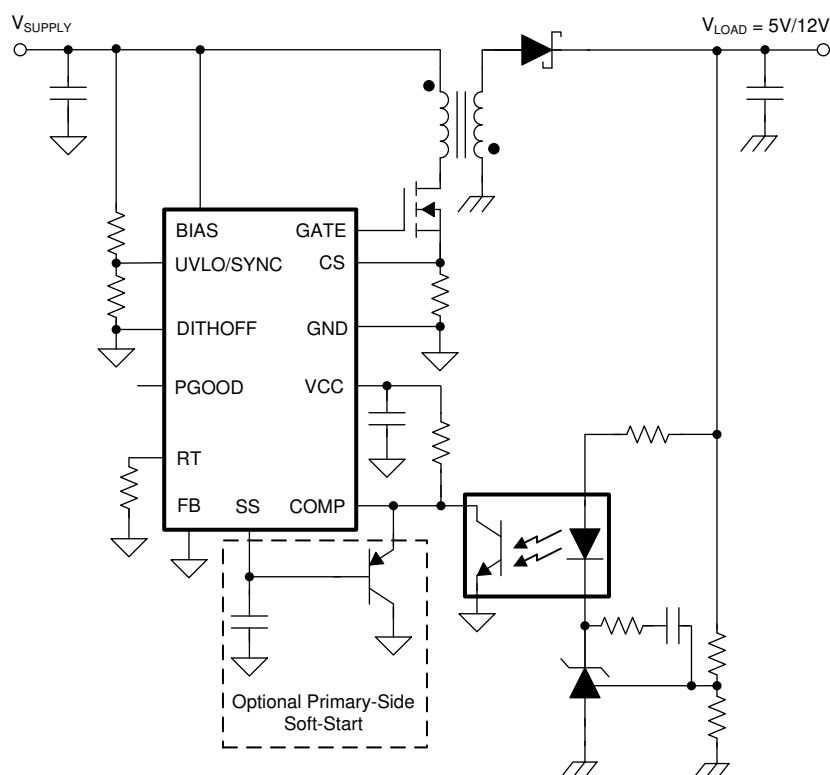


图 10-10. Secondary-Side Regulated Isolated Flyback

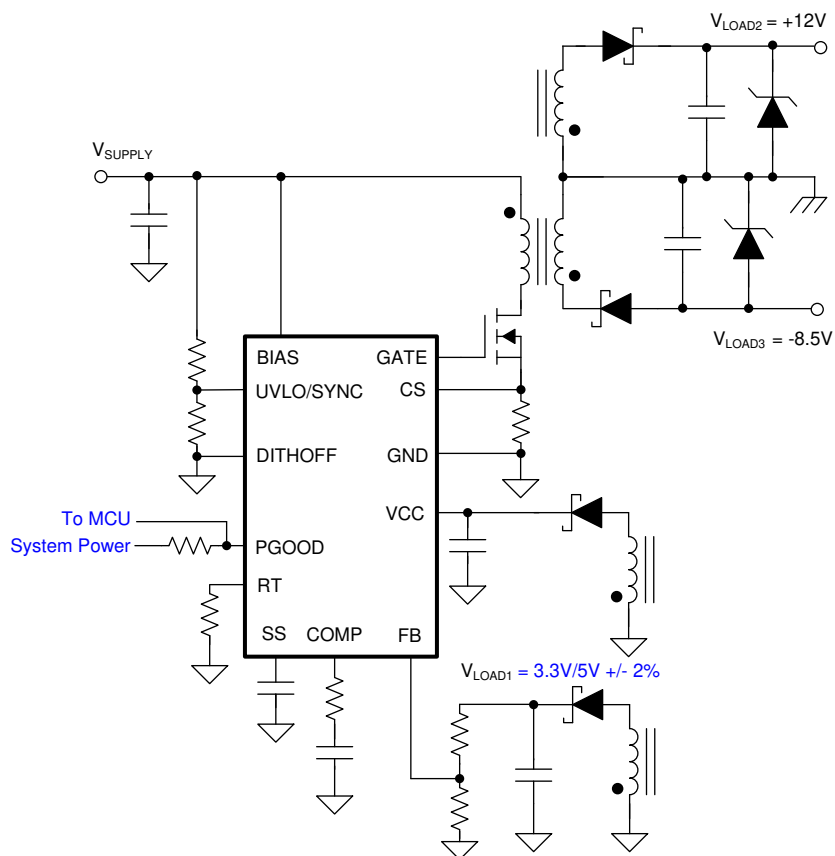


图 10-11. Primary-Side Regulated Multiple-Output Isolated Flyback

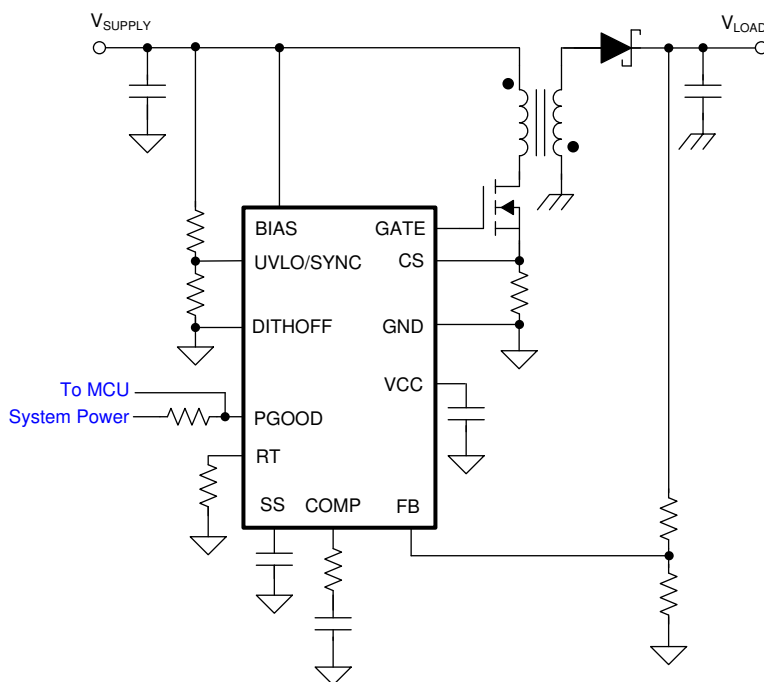


图 10-12. Typical Non-Isolated Flyback

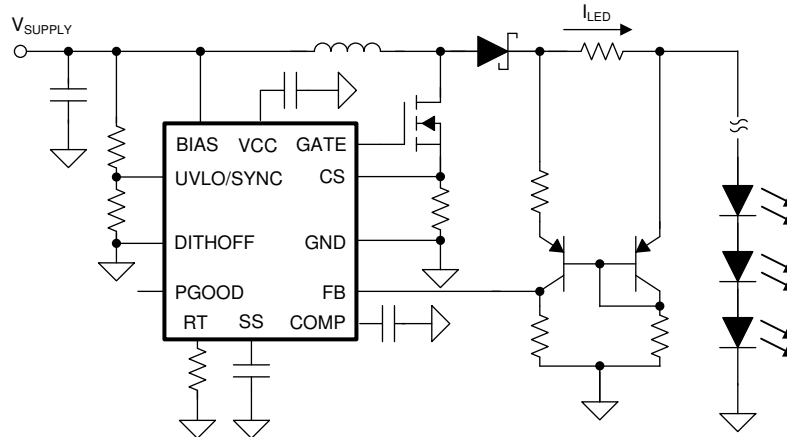


图 10-13. LED Driver with High-Side Current Sensing

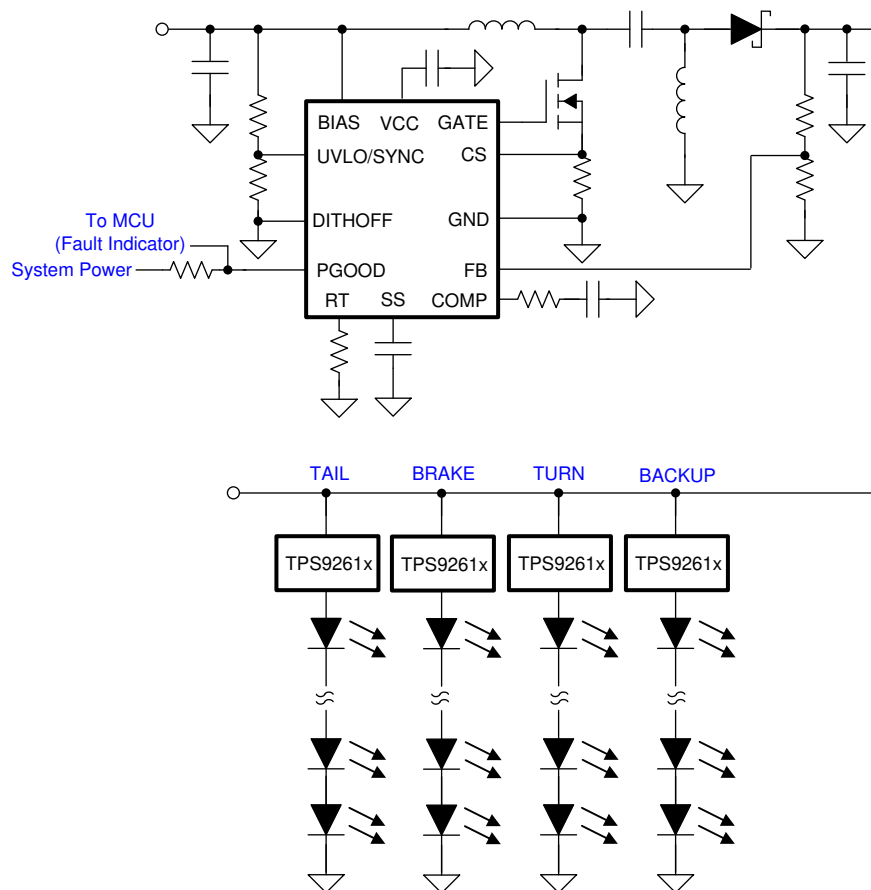


图 10-14. Dual-Stage Automotive Rear-Lights LED Driver

## 11 Power Supply Recommendations

The device is designed to operate from a power supply or a battery whose voltage range is from 1.5 V to 60 V. The input power supply must be able to supply the maximum boost supply voltage and handle the maximum input current at 1.5 V. The impedance of the power supply and battery including cables must be low enough that an input current transient does not cause an excessive drop. Additional input ceramic capacitors can be required at the supply input of the converter.

## 12 Layout

### 12.1 Layout Guidelines

The performance of switching converters heavily depends on the quality of the PCB layout. The following guidelines will help users design a PCB with the best power conversion performance, thermal performance, and minimize generation of unwanted EMI.

- Put the Q1, D1, and  $R_S$  components on the board first.
- Use a small size ceramic capacitor for  $C_{OUT}$ .
- Make the switching loop ( $C_{OUT}$  to D1 to Q1 to  $R_S$  to  $C_{OUT}$ ) as small as possible.
- Leave a copper area near the D1 diode for thermal dissipation.
- Put the device near the  $R_S$  resistor.
- Put the  $C_{VCC}$  capacitor as near the device as possible between the VCC and GND pins.
- Use a wide and short trace to connect the GND pin directly to the center of the sense resistor.
- Connect the CS pin to the center of the sense resistor. If necessary, use vias.
- Connect a filter capacitor between CS pin and power ground trace.
- Connect the COMP pin to the compensation components ( $R_{COMP}$  and  $C_{COMP}$ ).
- Connect the  $C_{COMP}$  capacitor to the power ground trace.
- Connect the GND pin directly to the analog ground plane. Connect the GND pin to the  $R_{UVLOB}$ ,  $R_T$ ,  $C_{SS}$ , and  $R_{FBB}$  components.
- Connect the exposed pad to the GND pin under the device.
- Connect the GATE pin to the gate of the Q1 FET. If necessary, use vias.
- Make the switching signal loop (GATE to Q1 to  $R_S$  to GND to GATE) as small as possible.
- Add several vias under the exposed pad to help conduct heat away from the device. Connect the vias to a large ground plane on the bottom layer.

## 12.2 Layout Examples

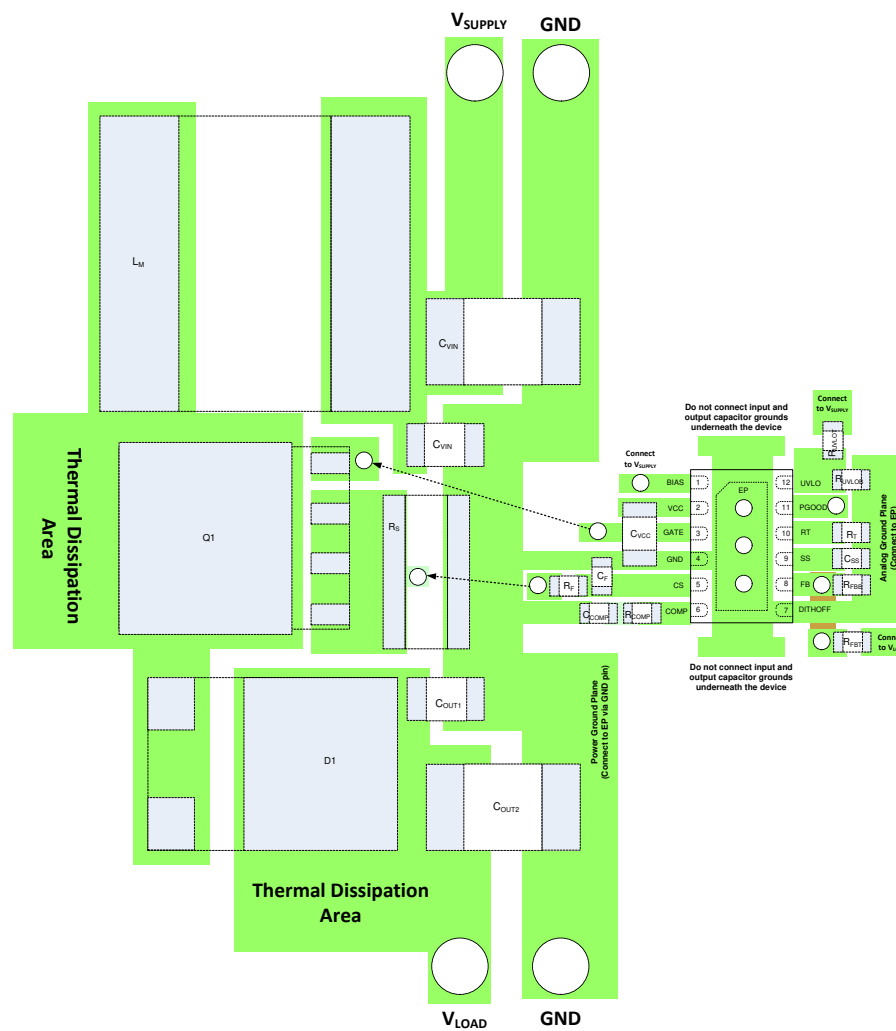


图 12-1. PCB Layout Example 1

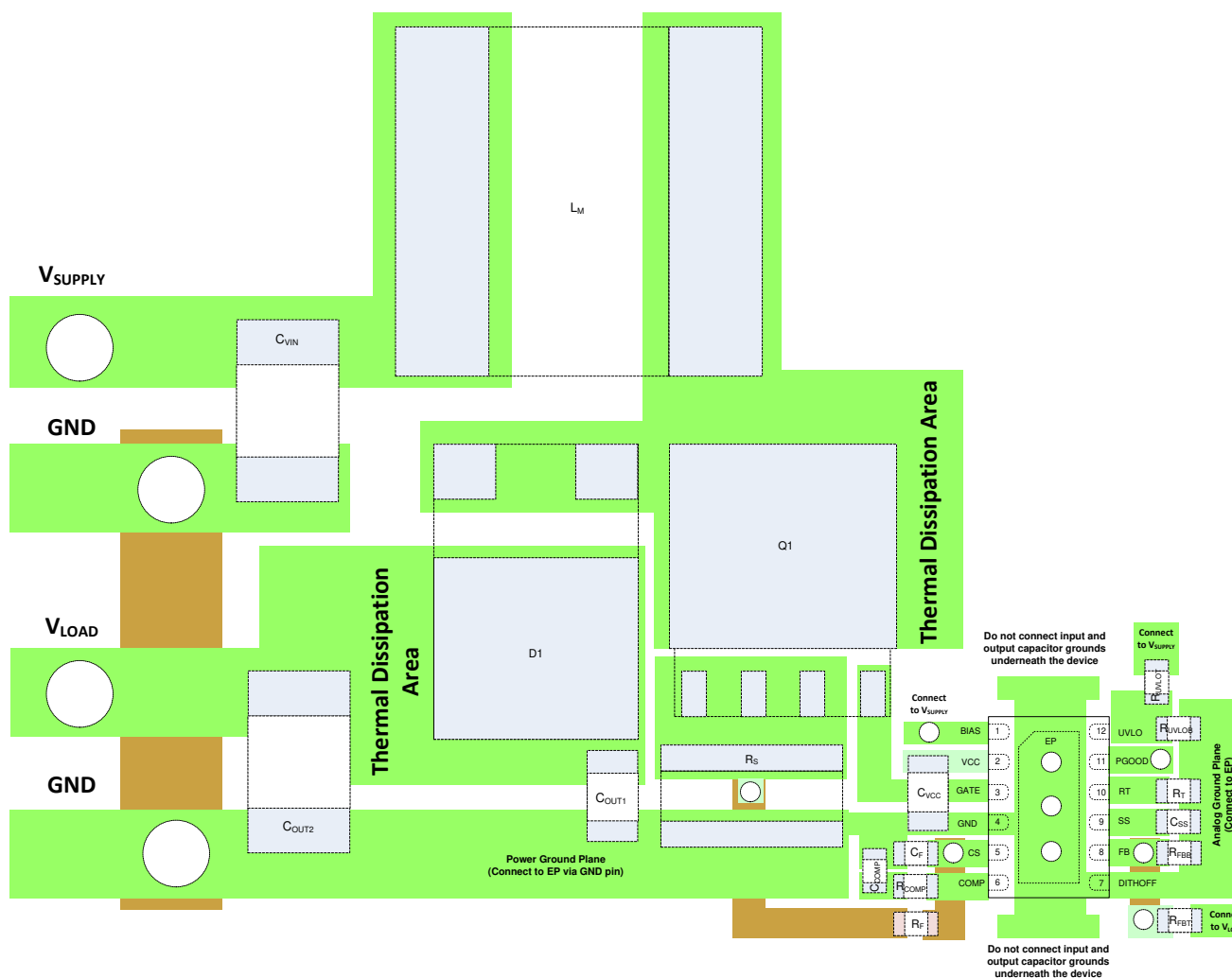


图 12-2. PCB Layout Example 2

## 13 Device and Documentation Support

### 13.1 Device Support

#### 13.1.1 第三方产品免责声明

TI 发布的与第三方产品或服务有关的信息，不能构成与此类产品或服务或保修的适用性有关的认可，不能构成此类产品或服务单独或与任何 TI 产品或服务一起的表示或认可。

#### 13.1.2 Development Support

For development support see the following:

- [LM5155x / LM5156x Boost Quick Start Calculator](#)
- [LM5155x / LM5156x SEPIC Quick Start Calculator](#)
- [LM5155x / LM5156x Flyback Quick Start Calculator](#)

##### 13.1.2.1 Custom Design With WEBENCH® Tools

[Click here](#) to create a custom design using the LM5156x device with the WEBENCH® Power Designer.

1. Start by entering the input voltage ( $V_{IN}$ ), output voltage ( $V_{OUT}$ ), and output current ( $I_{OUT}$ ) requirements.
2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at [www.ti.com/WEBENCH](http://www.ti.com/WEBENCH).

### 13.2 Documentation Support

#### 13.2.1 Related Documentation

For related documentation see the following:

Texas Instruments, [LM5156EVM-BST User's Guide](#)

### 13.3 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](http://ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 13.4 支持资源

**TI E2E™ 支持论坛**是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

### 13.5 Trademarks

TI E2E™ is a trademark of Texas Instruments.

WEBENCH® is a registered trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

## 13.6 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

## 13.7 术语表

**TI 术语表**      本术语表列出并解释了术语、首字母缩略词和定义。



## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">LM51561DSSR</a>	Active	Production	WSO (DSS)   12	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2GAH
LM51561DSSR.A	Active	Production	WSO (DSS)   12	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2GAH
<a href="#">LM5156DSSR</a>	Active	Production	WSO (DSS)   12	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2FUH
LM5156DSSR.A	Active	Production	WSO (DSS)   12	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2FUH

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF LM5156, LM51561 :**

- Automotive : [LM5156-Q1](#), [LM51561-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

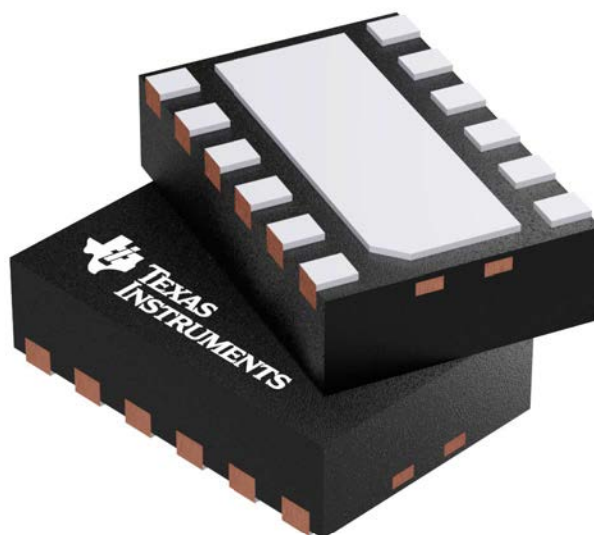
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM51561DSSR	WSO	DSS	12	3000	180.0	8.4	2.25	3.25	1.05	4.0	8.0	Q1
LM5156DSSR	WSO	DSS	12	3000	180.0	8.4	2.25	3.25	1.05	4.0	8.0	Q1

## TAPE AND REEL BOX DIMENSIONS

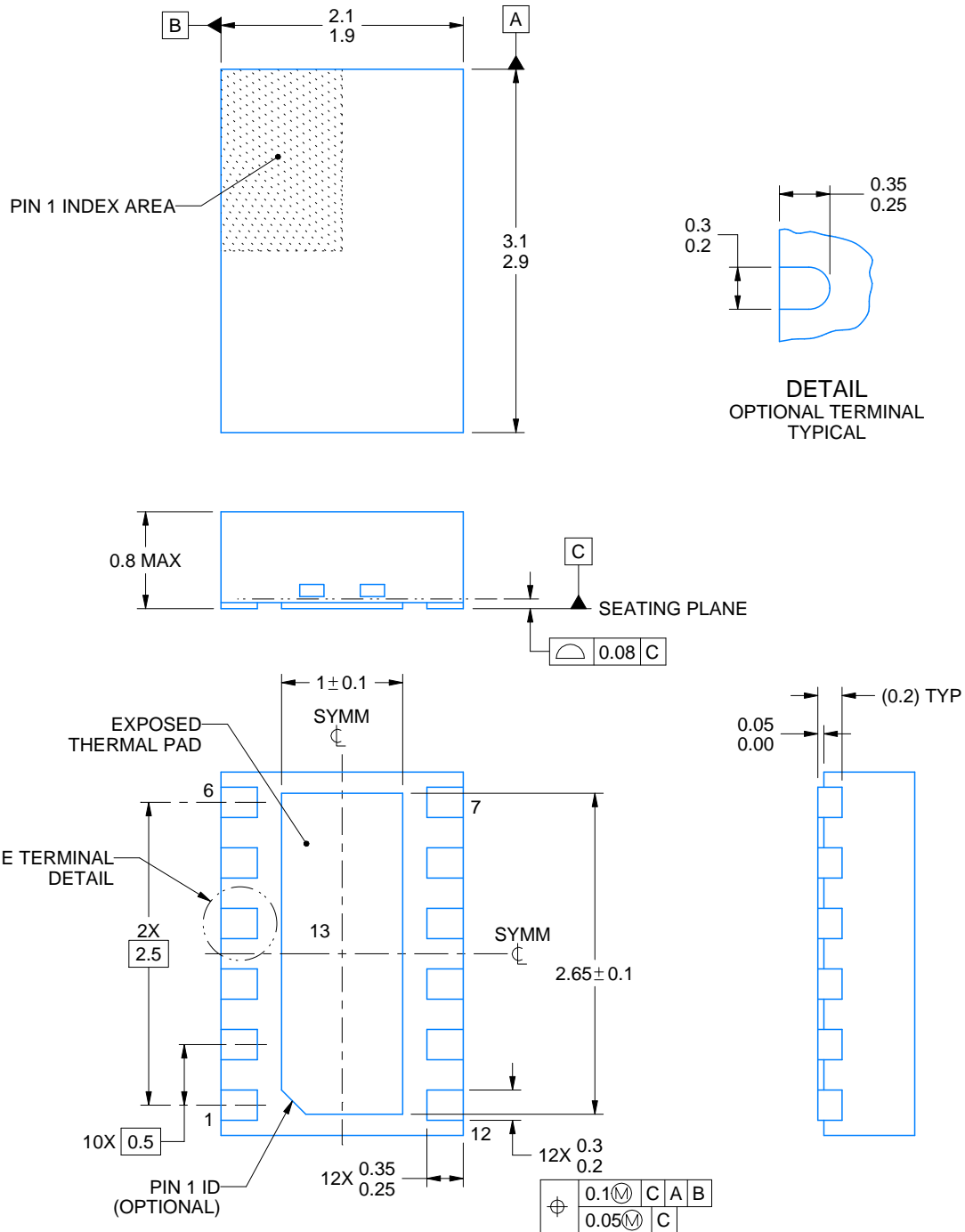
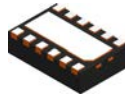


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM51561DSSR	WSON	DSS	12	3000	210.0	185.0	35.0
LM5156DSSR	WSON	DSS	12	3000	210.0	185.0	35.0



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



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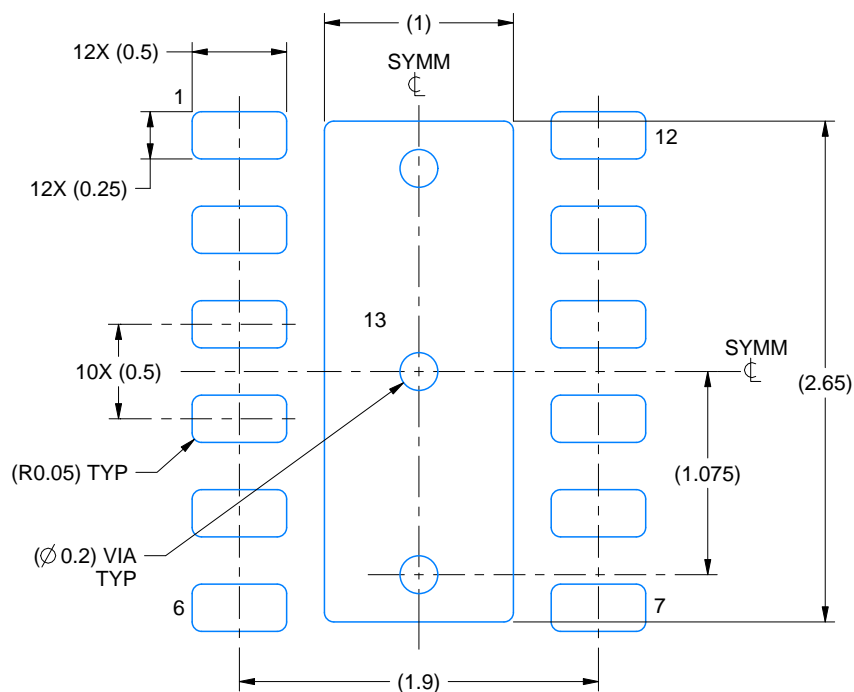
## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

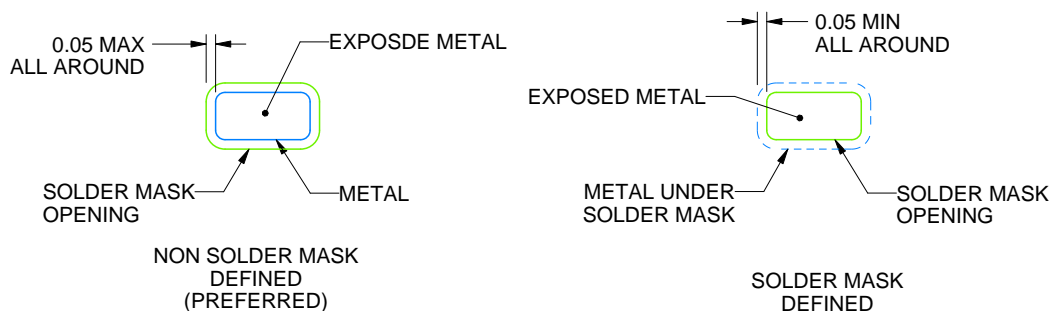
**DSS0012B**

**WSON - 0.8 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:25X



## SOLDER MASK DETAILS

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NOTES: (continued)

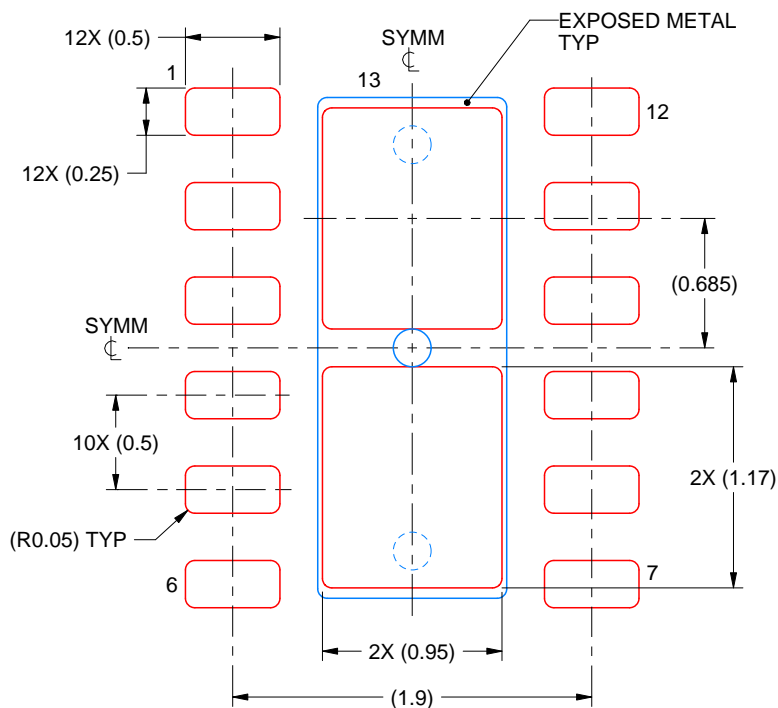
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



**DSS0012B**

**WSON - 0.8 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



## SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 13:  
83% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
SCALE:25X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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